



Radiation Detector developments for low- and medium- energy photons

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on behalf of the DESY FS-DS group
and collaboration partners





In a glance



A.G.I.P.D.

(Adaptive Gain Integrating Pixel Detector)

- European X-FEL, Petra P01/10
- ~12keV photons
- single photon upto $\sim 10^4$ photons/pixel/frame
- 300e noise
- 1Mpixel, 200um pitch
- 4.5 Mframe/s (burst)
- hybrid Si-Si detector

P.E.R.C.I.V.A.L.

(Pixellated Energy Resolving Cmos Imager, Versatile And Large)

- Petra P04, Flash, low-En synch/FELs
- 250e V ~1keV photons
- target: single photon upto $10^4 \sim 10^5$ photons/pixel/frame
- target: <15e noise
- 10~16Mpixel, 25~27um pixel pitch
- 10-120 frame/s
- back-illuminated MAPS



European X-FEL



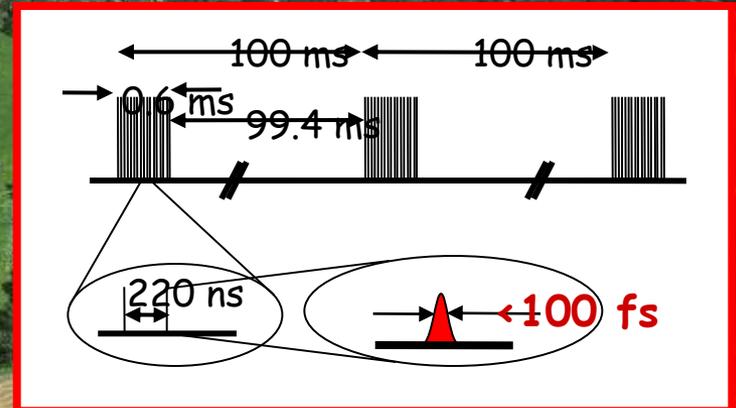
- Self-Amplified Spontaneous Emission
- e- accel. up to 17.5 GeV
- to 200m long undulators
- X-ray pulses produced

10^{33} ph/(s mm² mrad² 0.1%BW)
peak brilliance

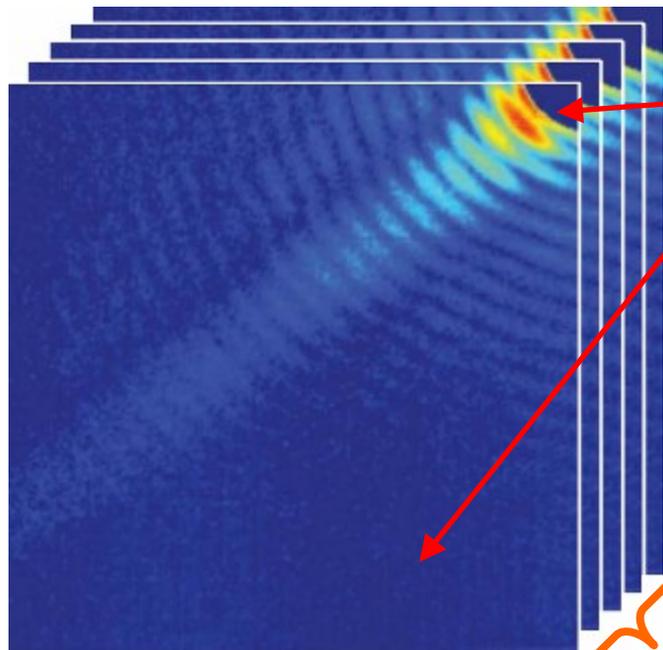
Non-uniform structure
2700 pulses @4.5MHz
every 100ms

Tunnel

- 3.4 km long
- 12-44 m deep



Constraints



in the same image:
• up to $\sim 10^4$ photons
• down to 0~1

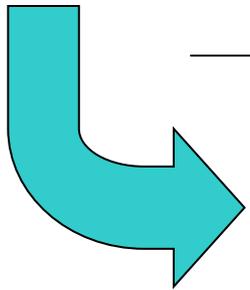
1-photon resolution!
(or better than poissonian)

single-image experiments!
as many as possible!

many pixels!
small pixels!

radiation
tolerant!

4.5MHz x
2700 images

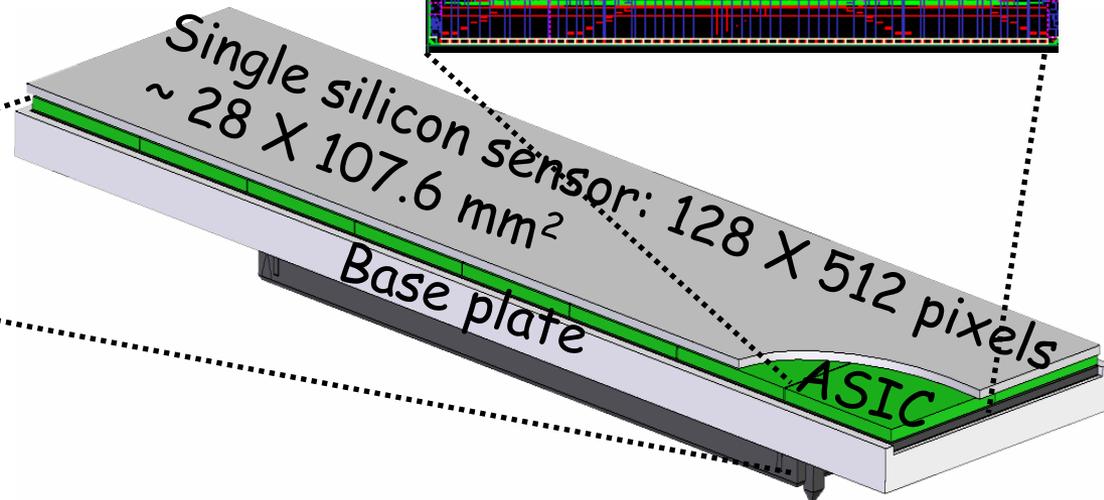
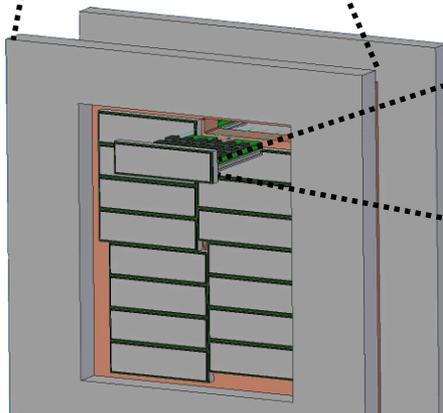
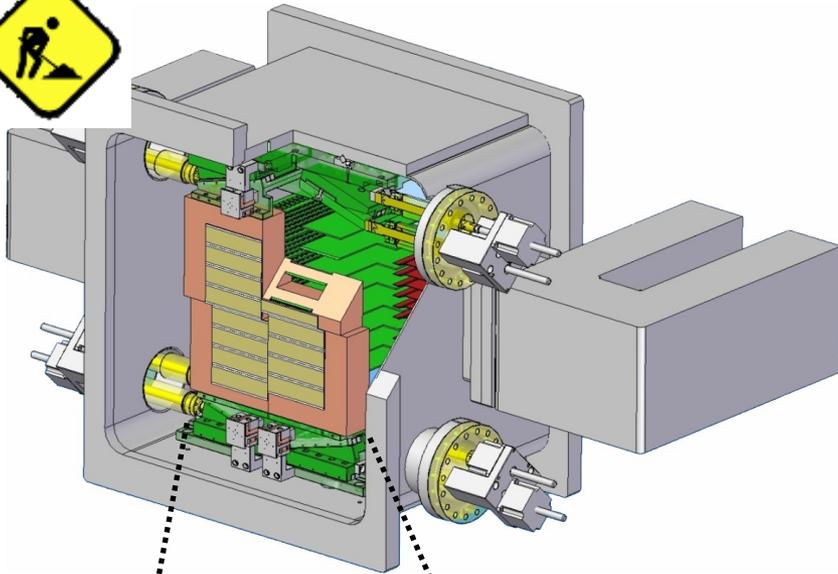


Charge integration
Adaptable Gain $O(2)$
noise ~ 0.1 photon
1Mpixel, 200 μm pitch
in-pixel Memory (352)

veto schema
leakage minimization
rad hard design



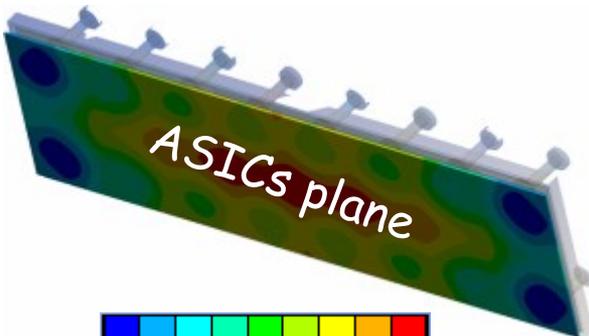
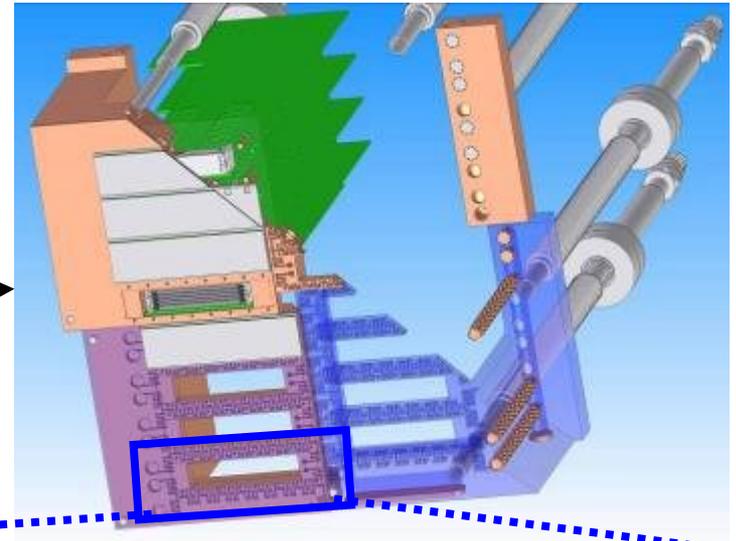
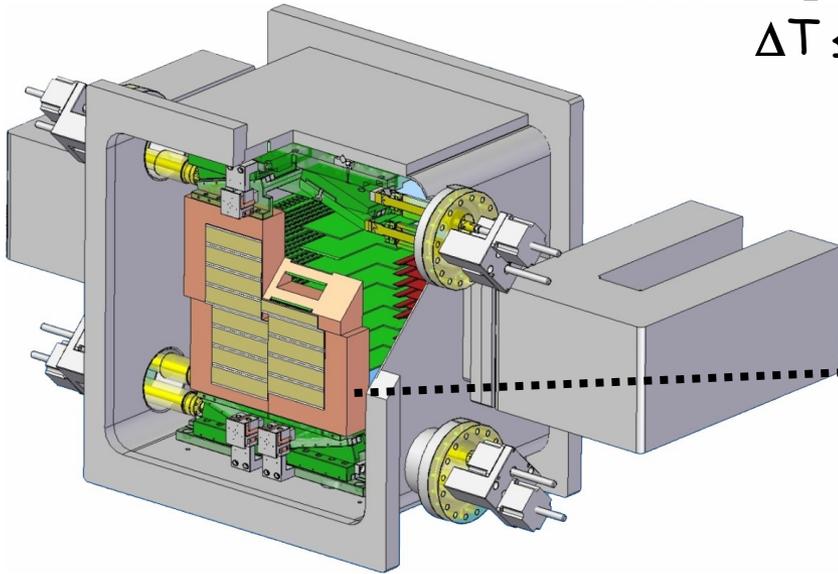
The A.G.I.P.D. (1_a assembly)



The A.G.I.P.D. (1C_{Cooling})

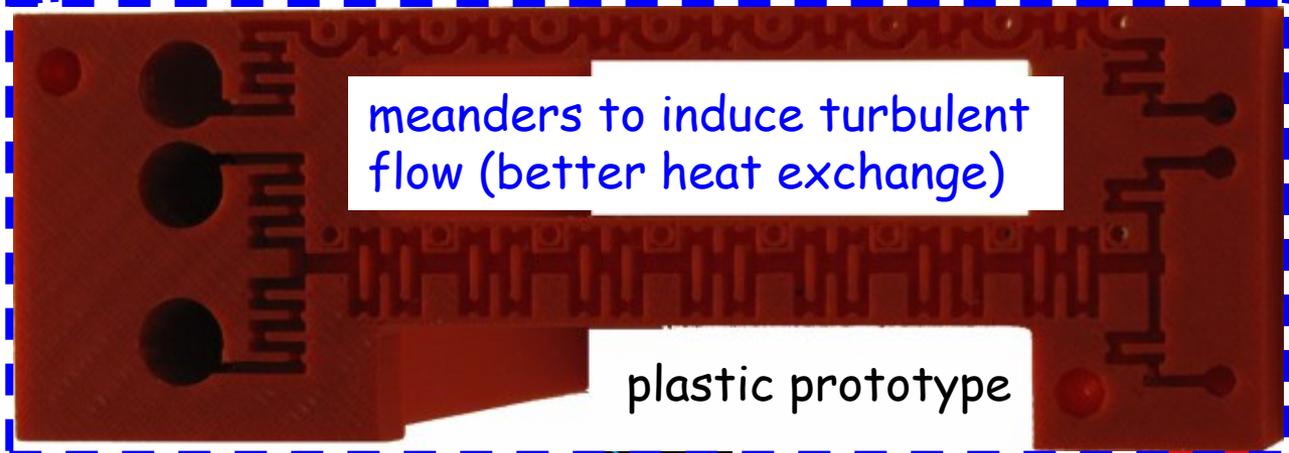


ASIC : $T \leq -20^{\circ}\text{C}$ (less droop post irradiation)
 $\Delta T \leq 5 \text{ K}$ (less spread parameters)



-24.1 °C to -20.4 °C
 $\Delta T = 3.7 \text{ K}$

meanders to induce turbulent flow (better heat exchange)



plastic prototype

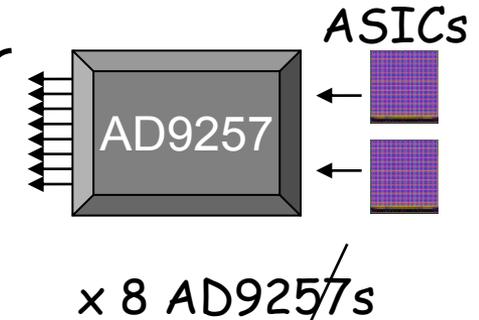
The A.G.I.P.D. (1_{data} out)



pixels	1M
mem cell/pixel	x 352
analog & gain	x2
bits/sample	x 14
in 100ms	x10

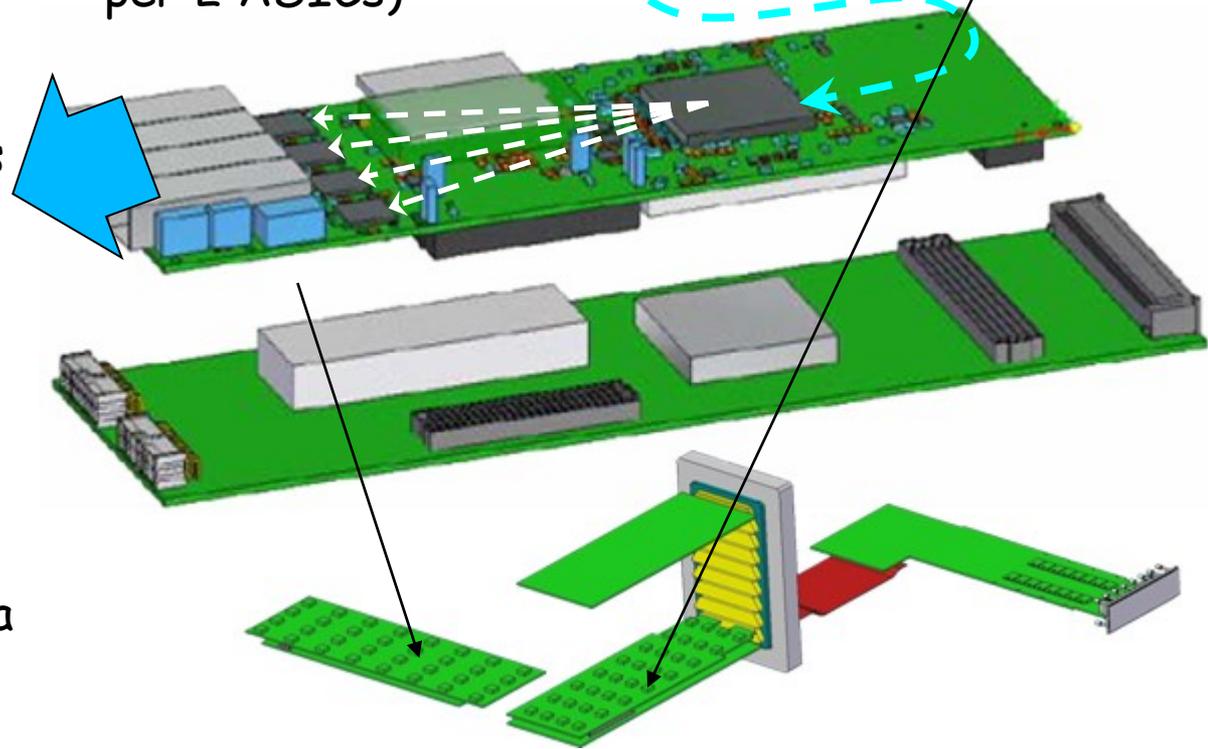
avg data rate	~96.5Gb/s

analog PCB: line reception, pickup noise filtering and digitization (@ 33MHz) 14 bits (8-channels AD9257, 1 per 2 ASICs)



each of the 16 module has its own "mezzanine" fast out board VIRTEX-5 FPGA: limited data sorting, pass data to 4x10 GbE outputs

data collected by data acquisition train builder card (receive, sort and reject data from the 1Mpixel camera)

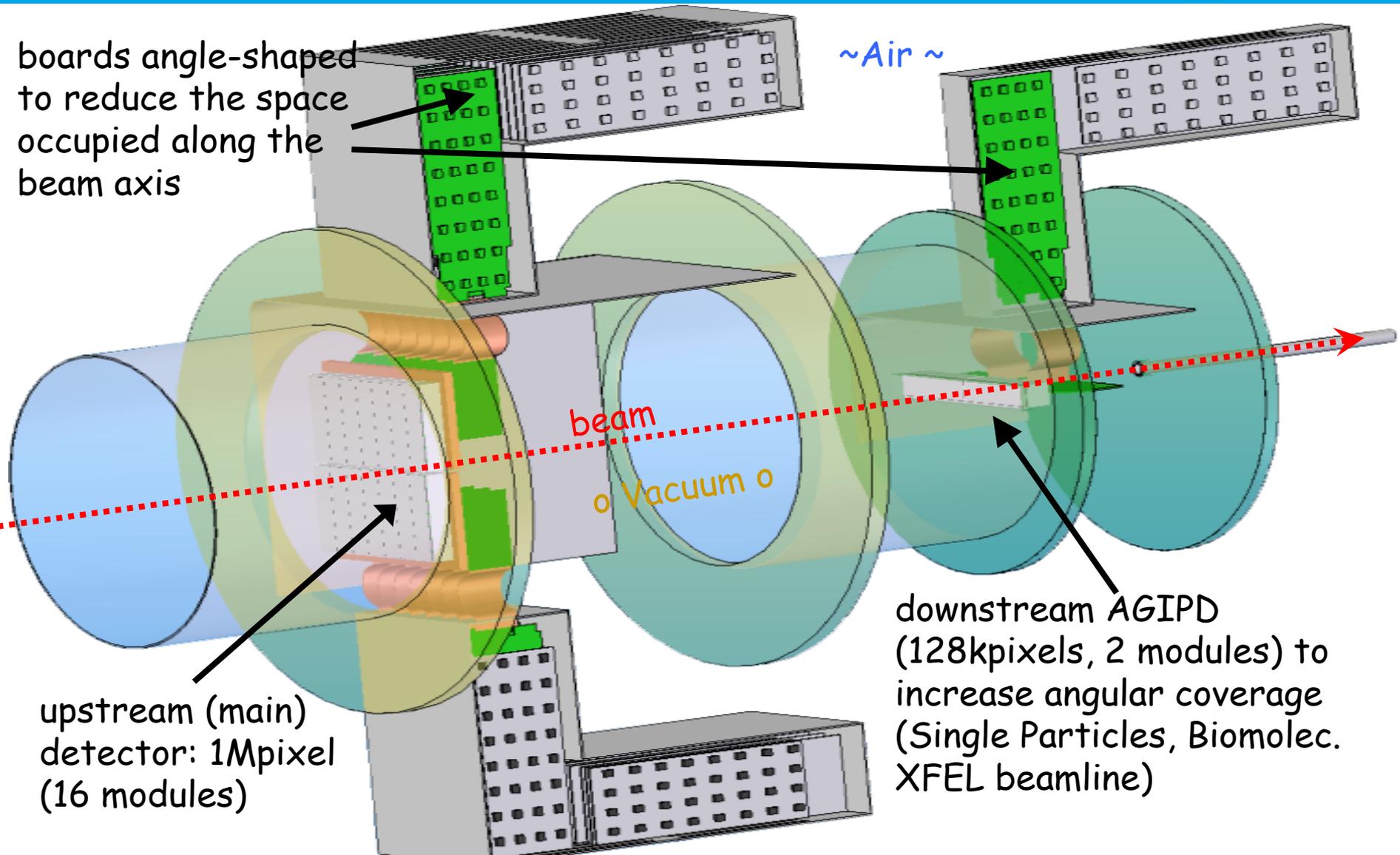


The A.G.I.P.D. (1_even 2 planes)



boards angle-shaped to reduce the space occupied along the beam axis

~Air~

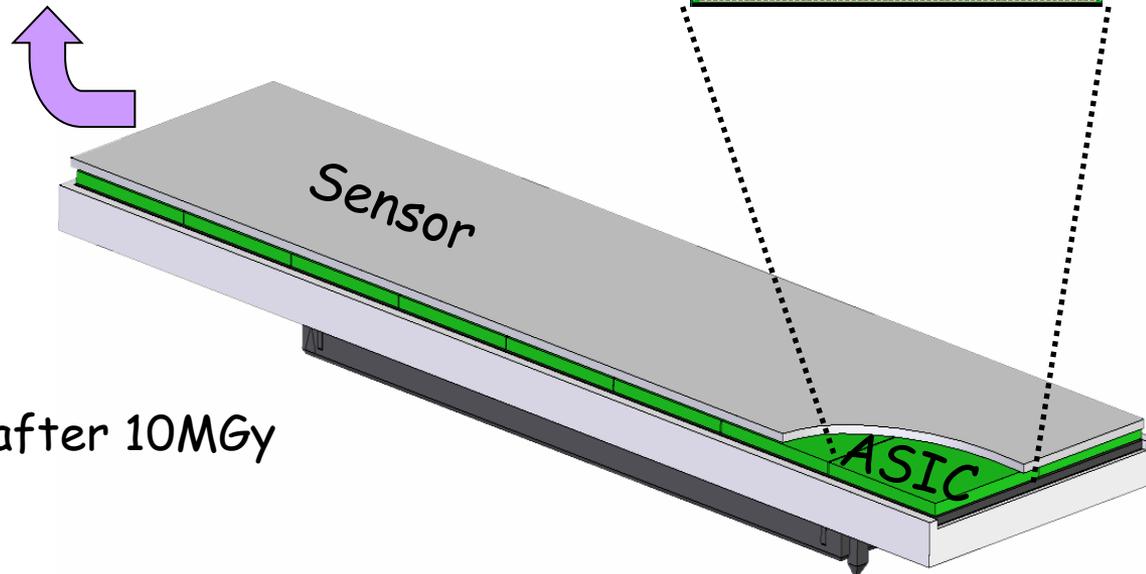
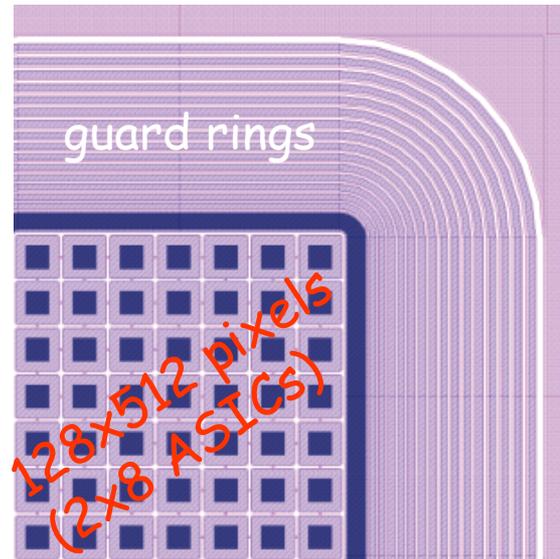


upstream (main) detector: 1Mpixel (16 modules)

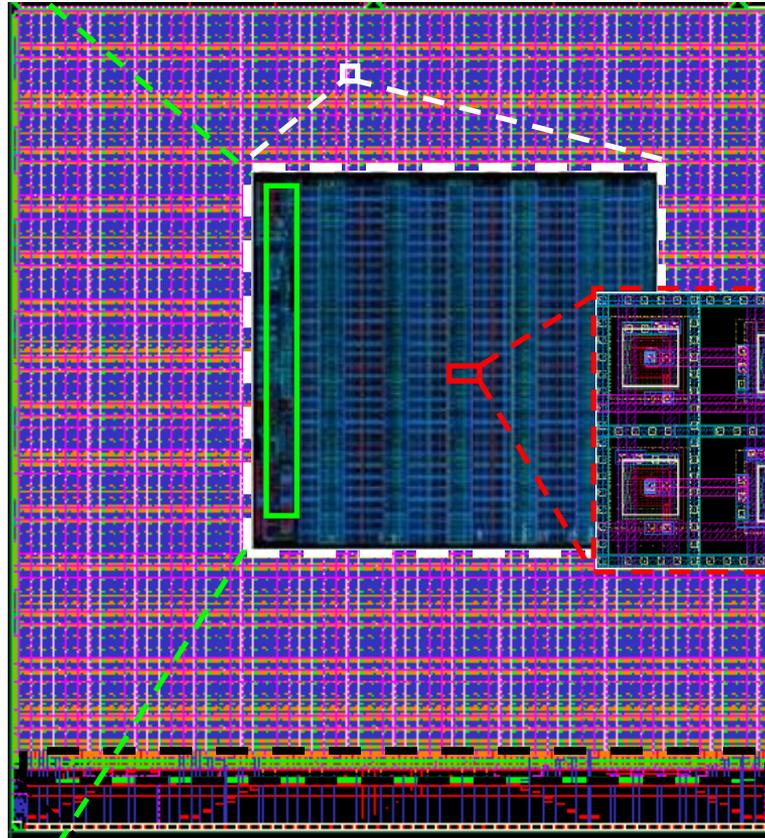
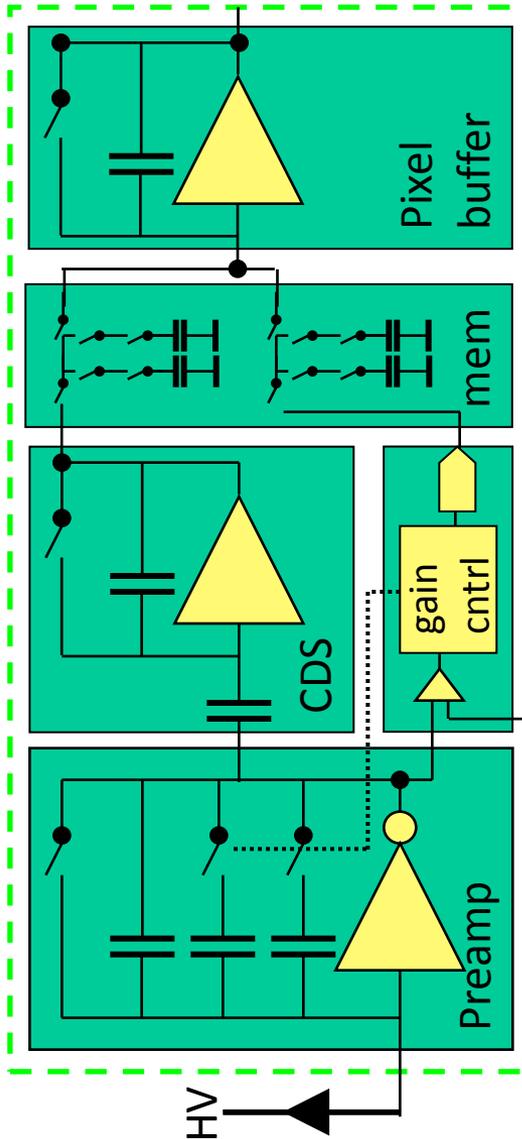
downstream AGIPD (128kpixels, 2 modules) to increase angular coverage (Single Particles, Biomolec. XFEL beamline)

The A.G.I.P.D. ($1f_{\text{ront}}$ sensor) AGIPD

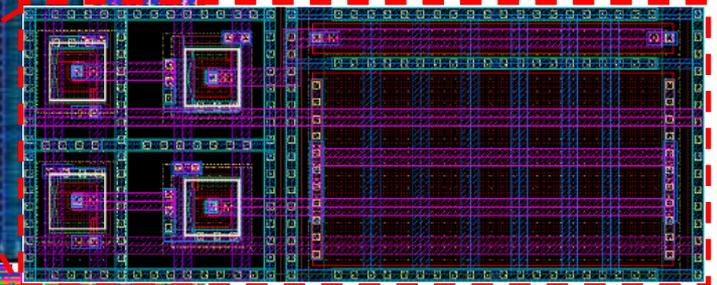
- Si sensor p+ over n (hole collection)
 - 107.6x28 mm (large monolithic sensors reduce the overall dead area)
 - 500um thick
 - ($>90\%$ QE @12.4keV)
 - effective entry window $<2.5\mu\text{m}$ (reasonable QE at lower energies)
 - bias voltage $>500\text{V}$ (minimizes impact plasma effects)
 - SINTEF tech
 - UniHH design
- rad-aware design: $B_d > 900\text{V}$ after 10MGy



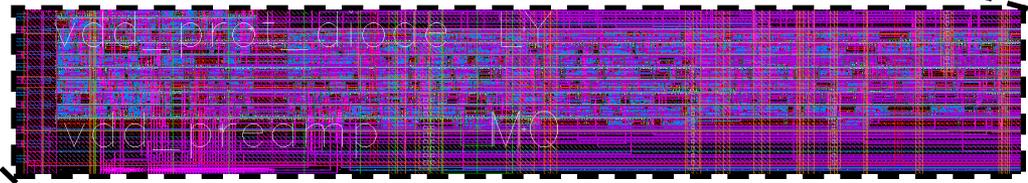
The A.G.I.P.D. (2)



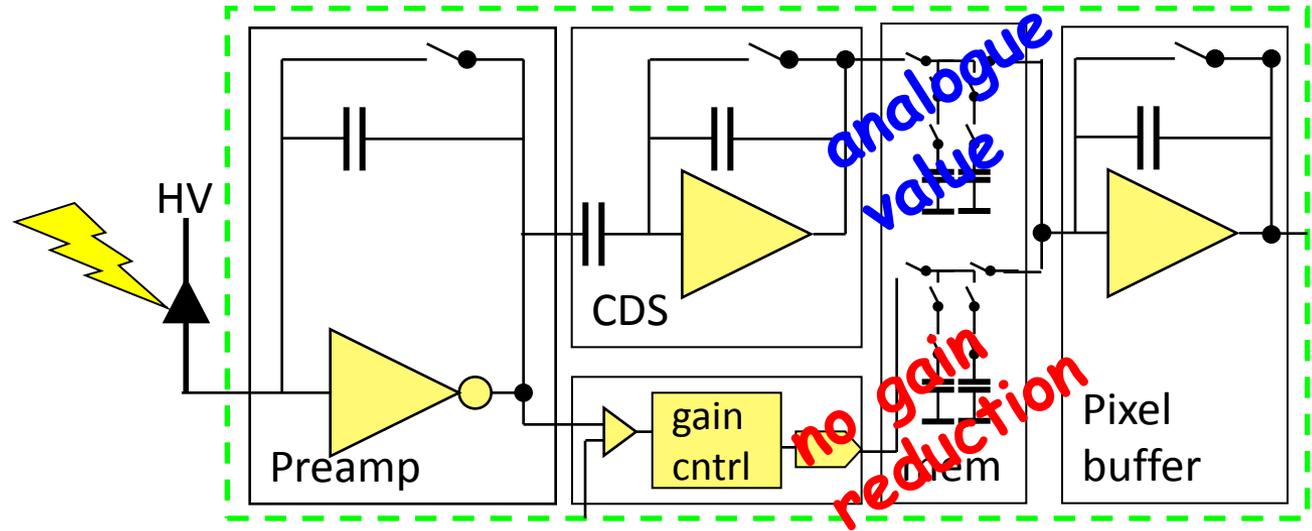
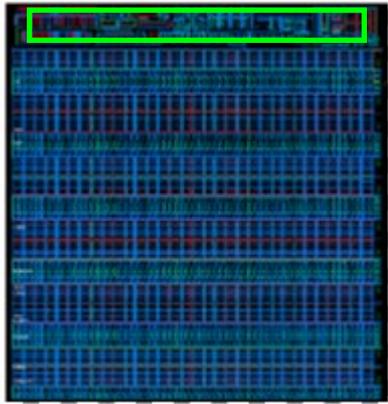
IBM 130 nm CMOS
64x64 pixels/ASIC
352 mem. cell/pixel



Command based
interface: 3 LVDS
lines + chipselect

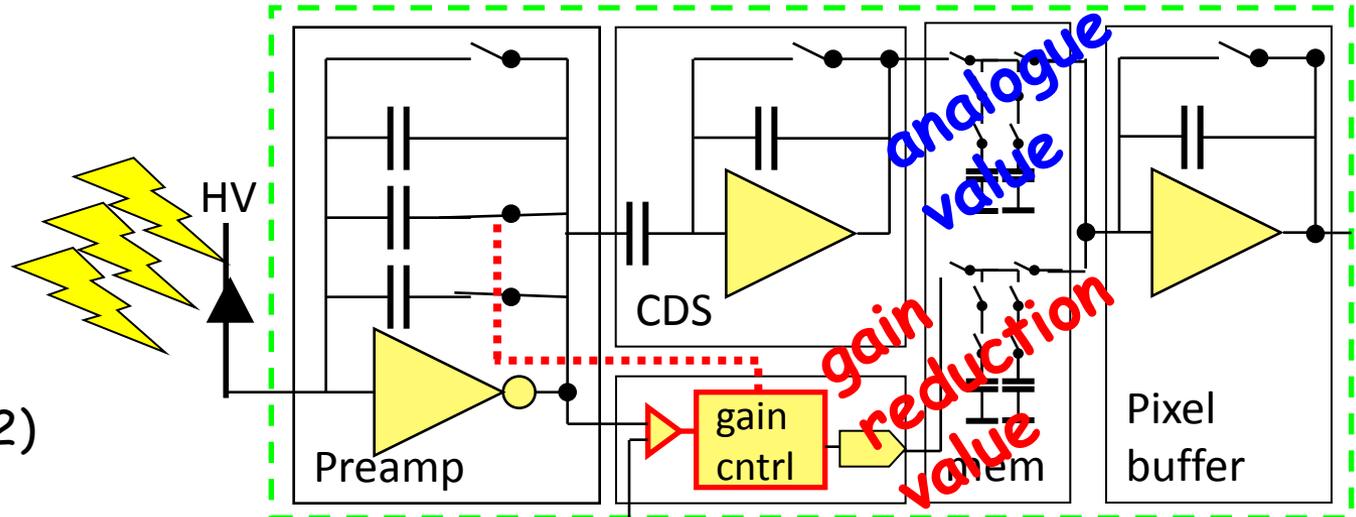


Adaptive Gain Concept

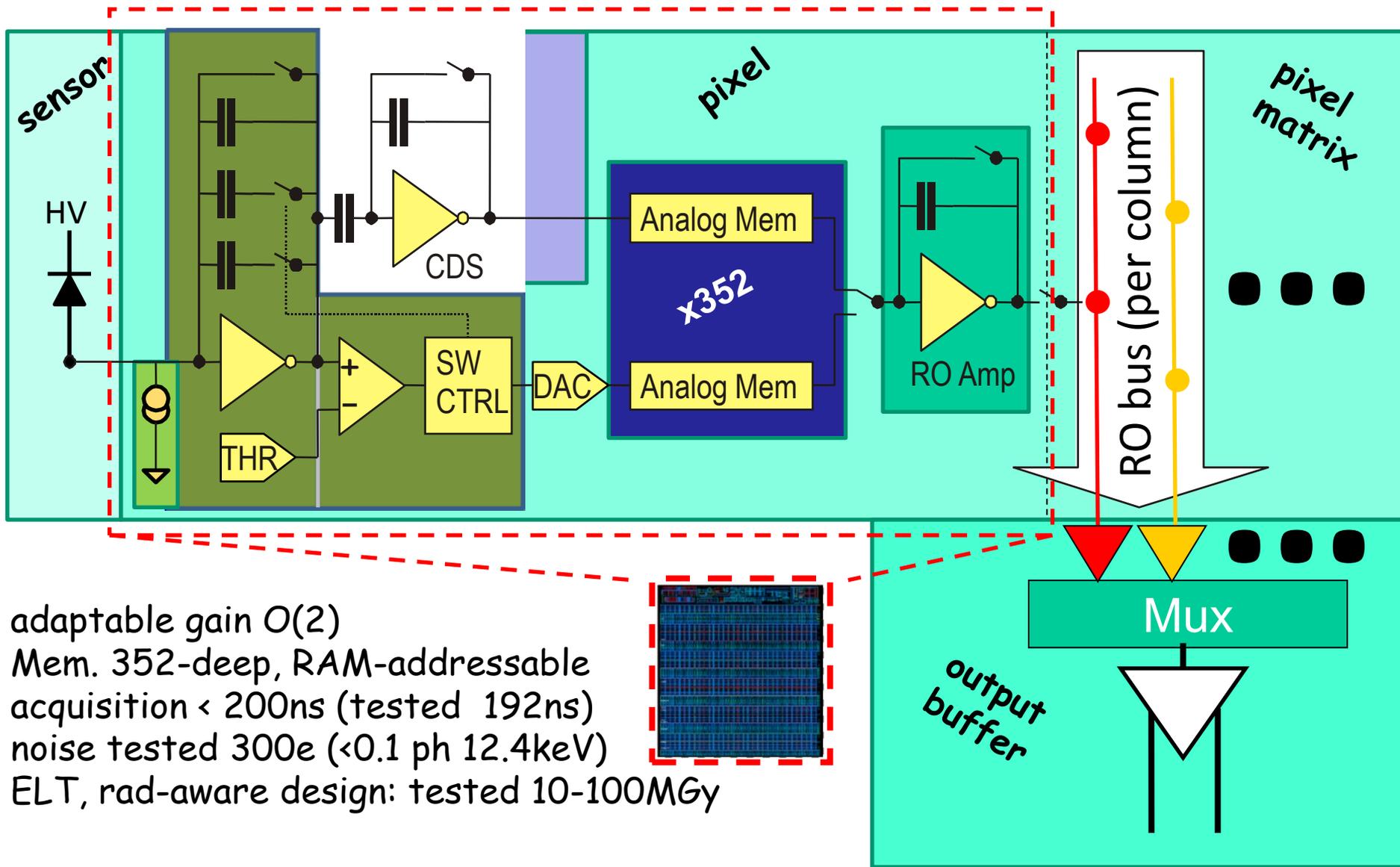


real-time adjustment
of the feedback
capacitance
depending on the
photon flux

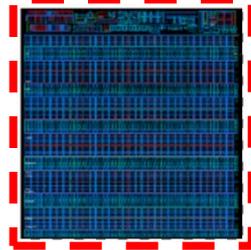
60fF/3fF/10fF dyn.
switching
=> adaptable gain $O(2)$



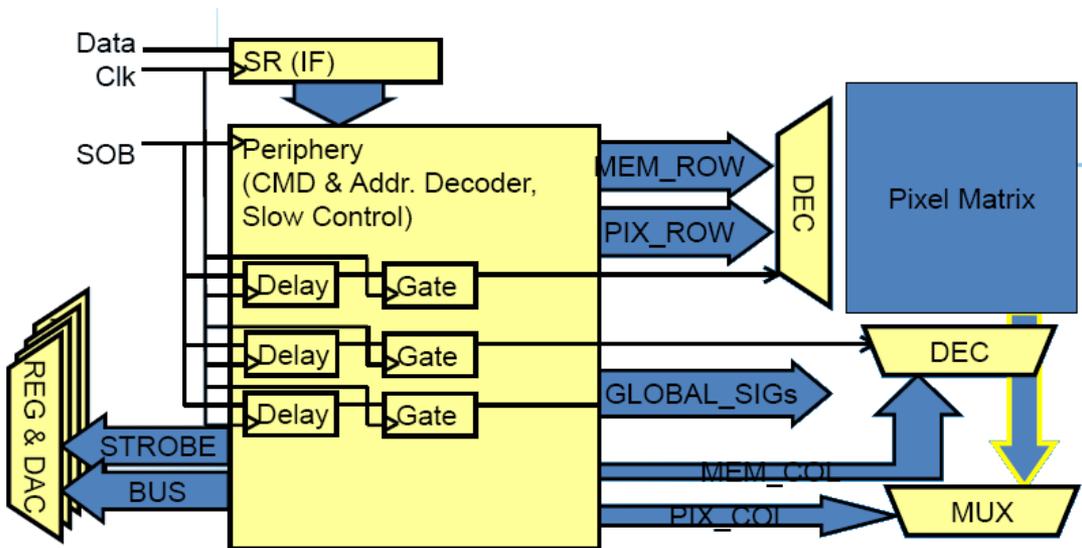
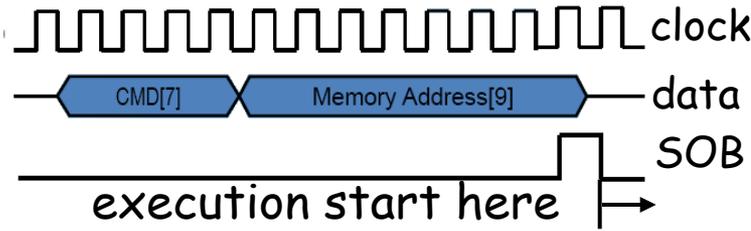
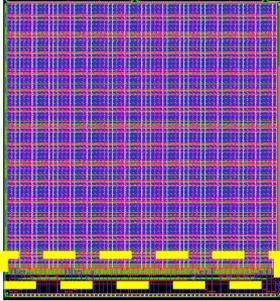
The A.G.I.P.D. (3)



adaptable gain $O(2)$
Mem. 352-deep, RAM-addressable
acquisition $< 200\text{ns}$ (tested 192ns)
noise tested $300e$ ($< 0.1\text{ ph } 12.4\text{keV}$)
ELT, rad-aware design: tested $10\text{-}100\text{MGy}$

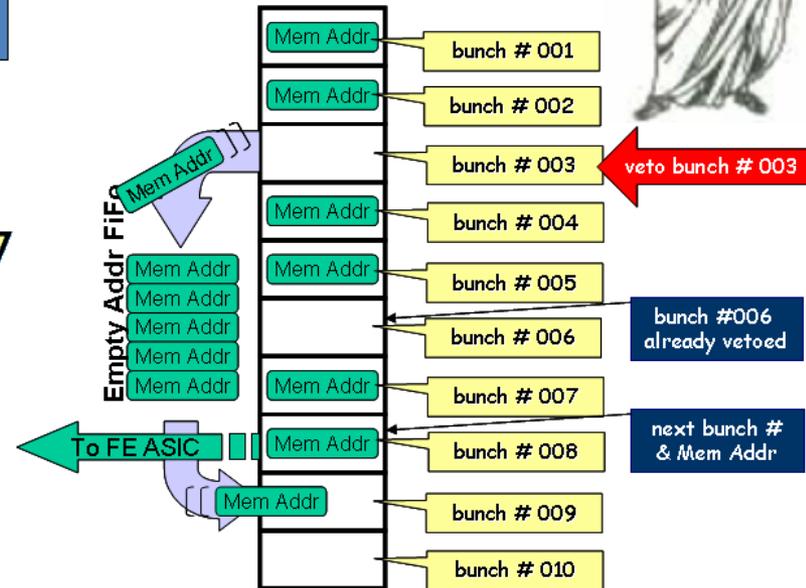


Command Serial IF



ARM cmrf8sf RVT SC Library
 Command Serial Interface
 3+1 LVDS Signals
 prototype working after 10MGy

Memory space addressable RAM-like from the (external) interface electronics allows for Veto schema (overwriting of meaningless data)

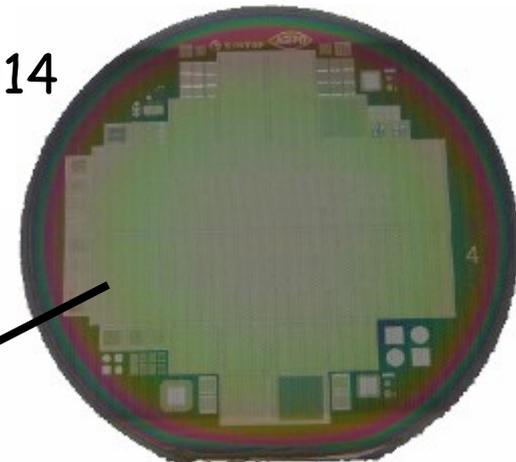
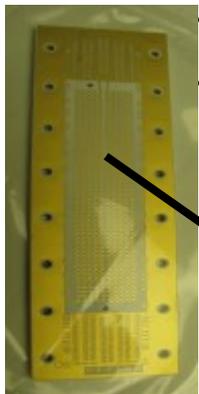


AGIPD 1.0 status

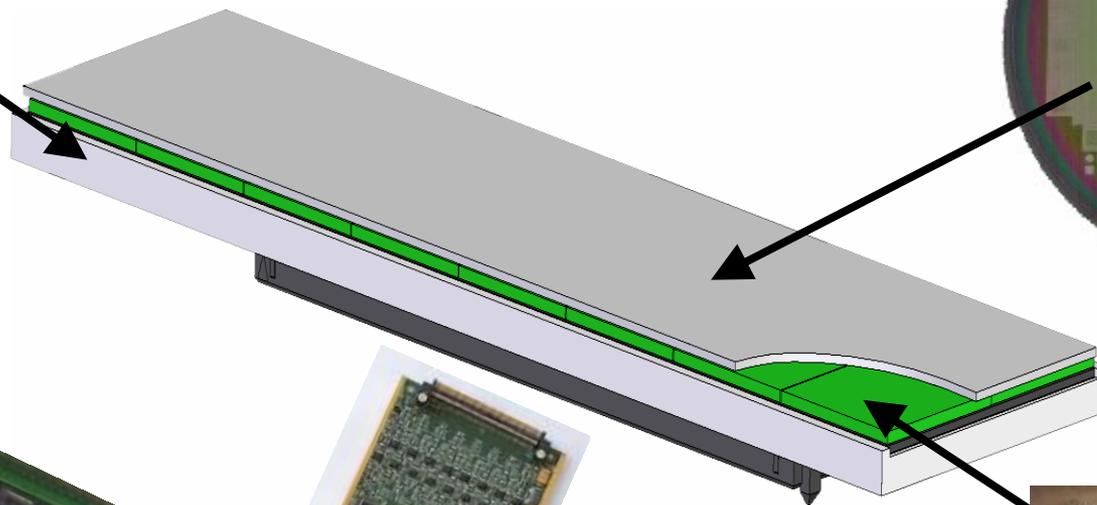


- Single chip assemblies: in a few weeks
- First modules (8x2 chips): beginning 2014
- First 1M system: beginning 2015

Low-T Co-fired
Ceramic board



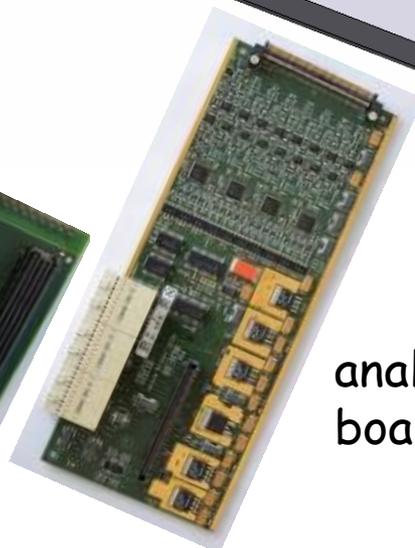
sensor



readout ASIC



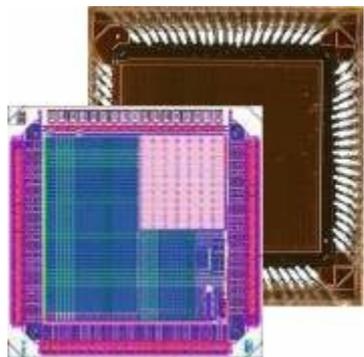
"mezzanine"
fast readout
board



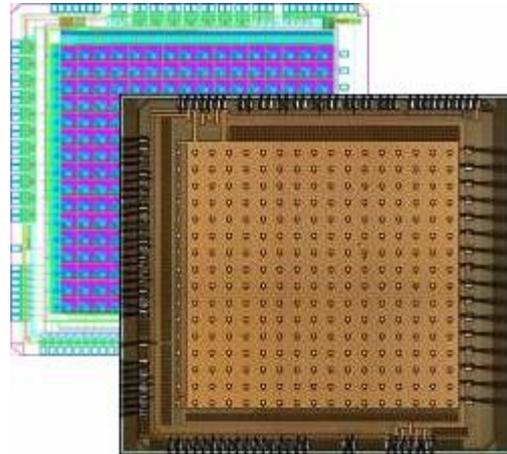
analogue mother
board (prot.)



former prototypes

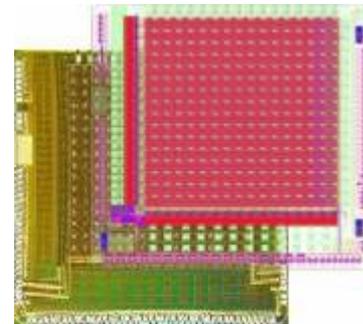


hpad1

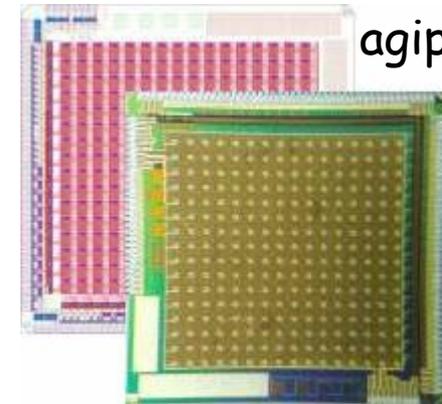


agipd04

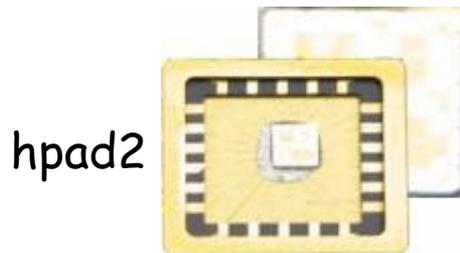
16x16 pixels
sub-opt. sensor



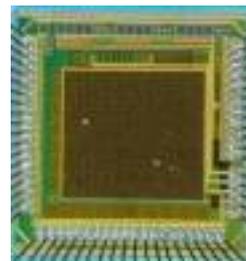
agipd03



agipd02



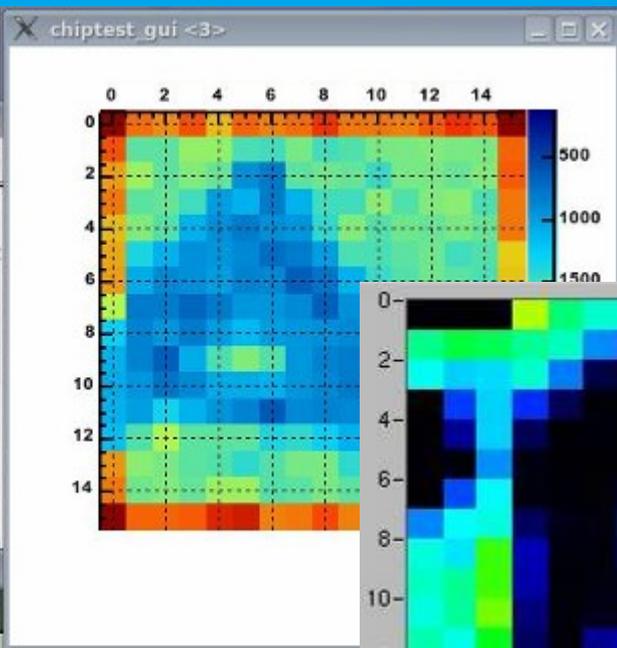
hpad2



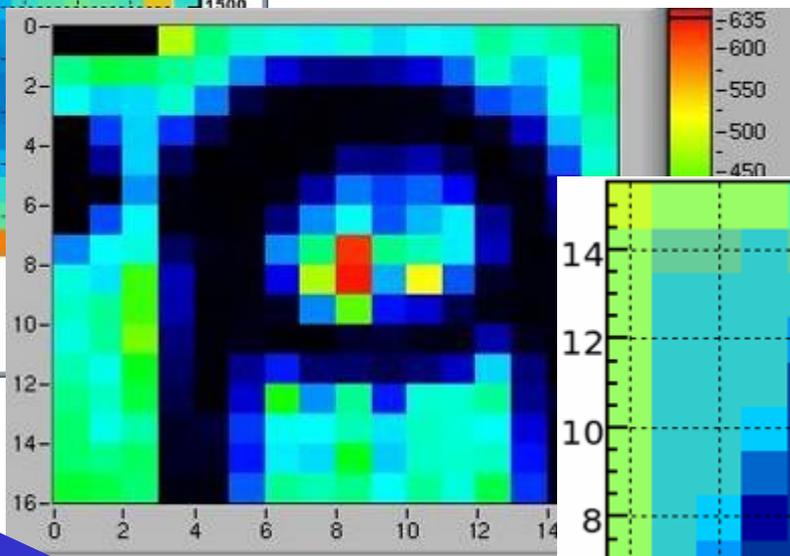
agipd01



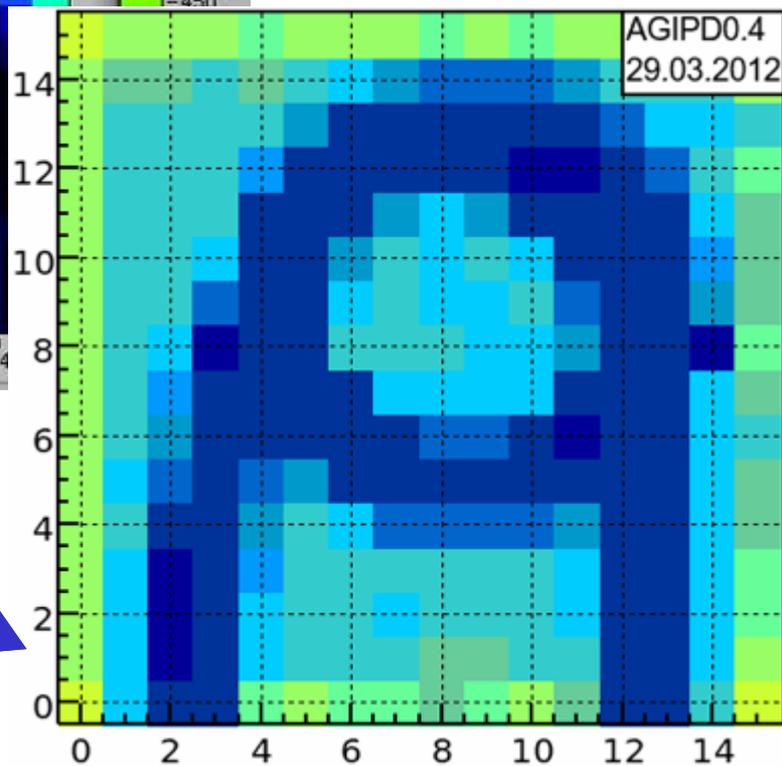
imaging with prototypes



AGIPD03

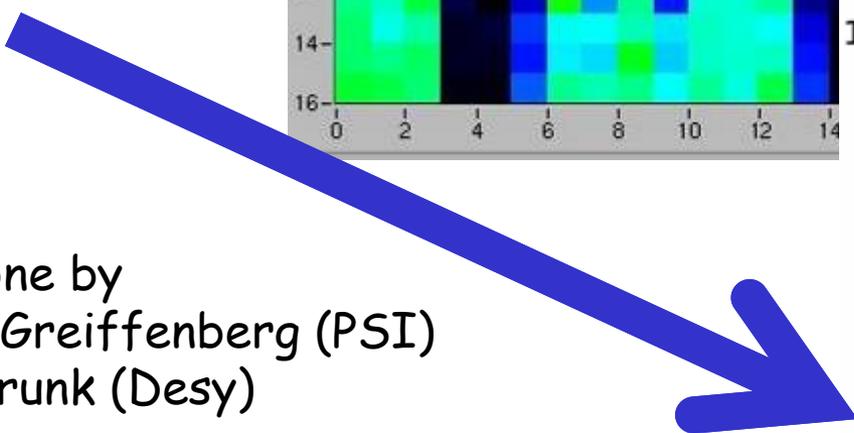


AGIPD04



AGIPD02

meas. done by
Dominic Greiffenberg (PSI)
Ulrich Trunk (Desy)

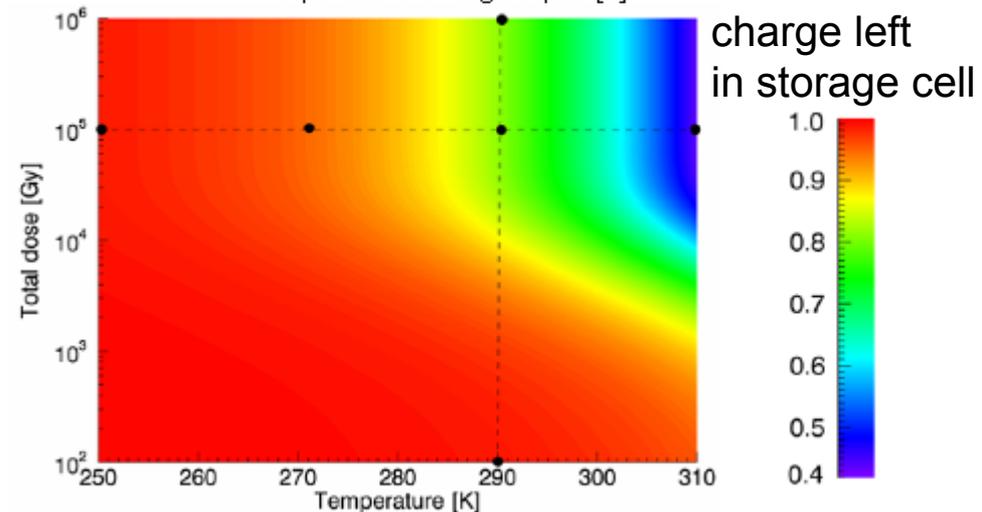
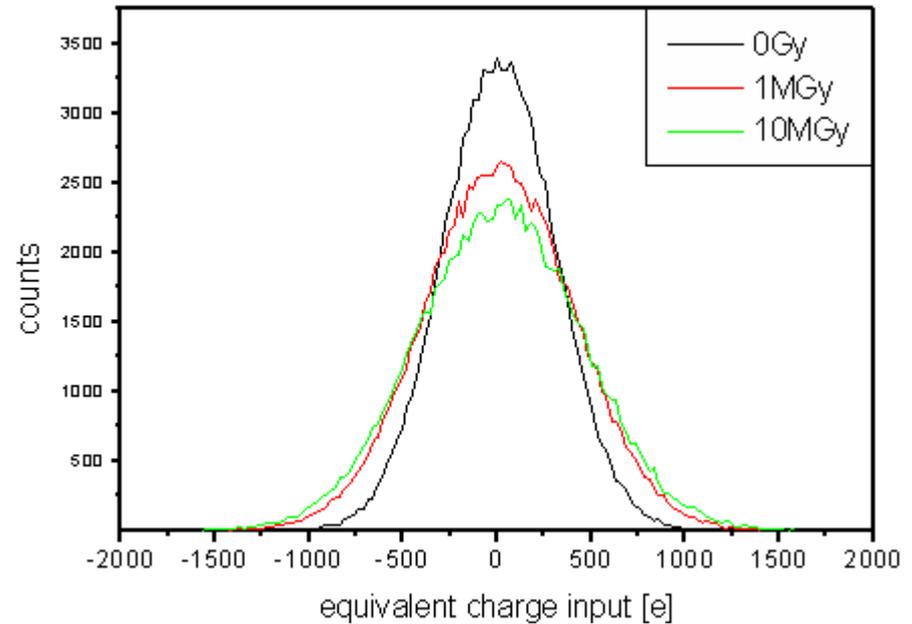


irradiating ASIC prot.



Irradiation of HPAD 0.1/0.2
AGIPD03/04 chips
up to 10-20-100MGy
@ DORIS F4
5.4kGy/s
highly accelerated
irradiation rate →
pessimistic estimation

- upto 10MGy: comparable behaviour, 30~40% noise increase
- 100MGy: functionality recover after annealing
- storage cell leakage (100ms): <1% at -20°C



irradiating sensor



Irradiation AGIPD sensor

up to 10MGy

@ Petra P11

12keV

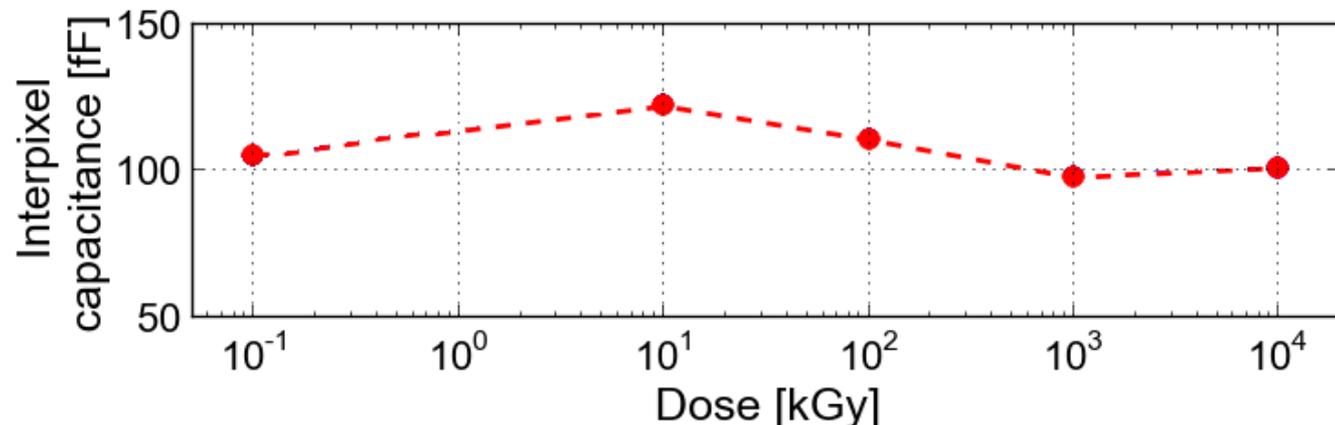
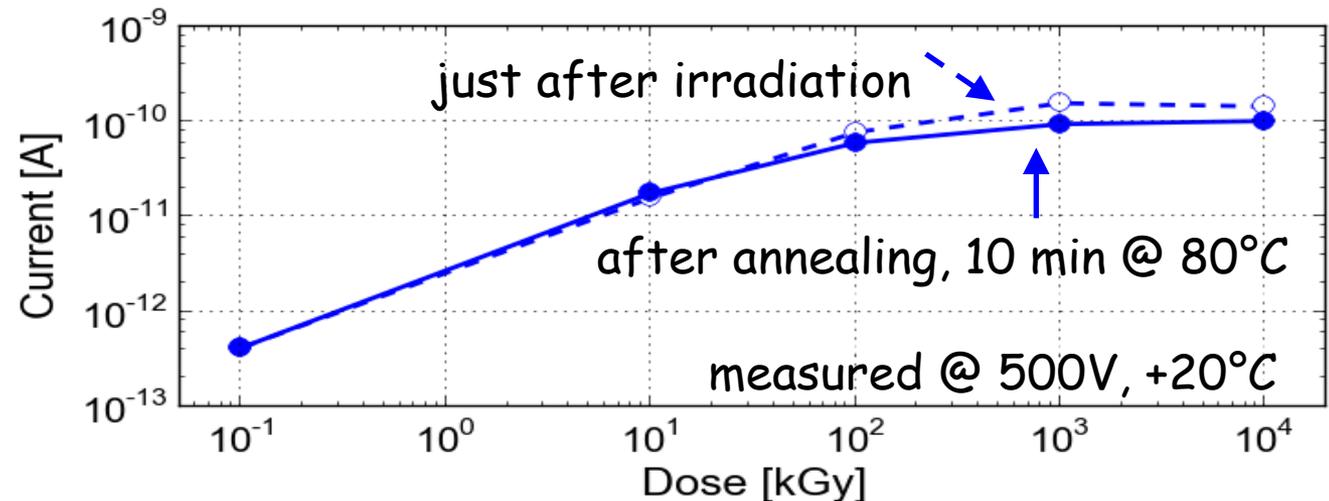
7.1kGy/s

J. Zhang et. al.

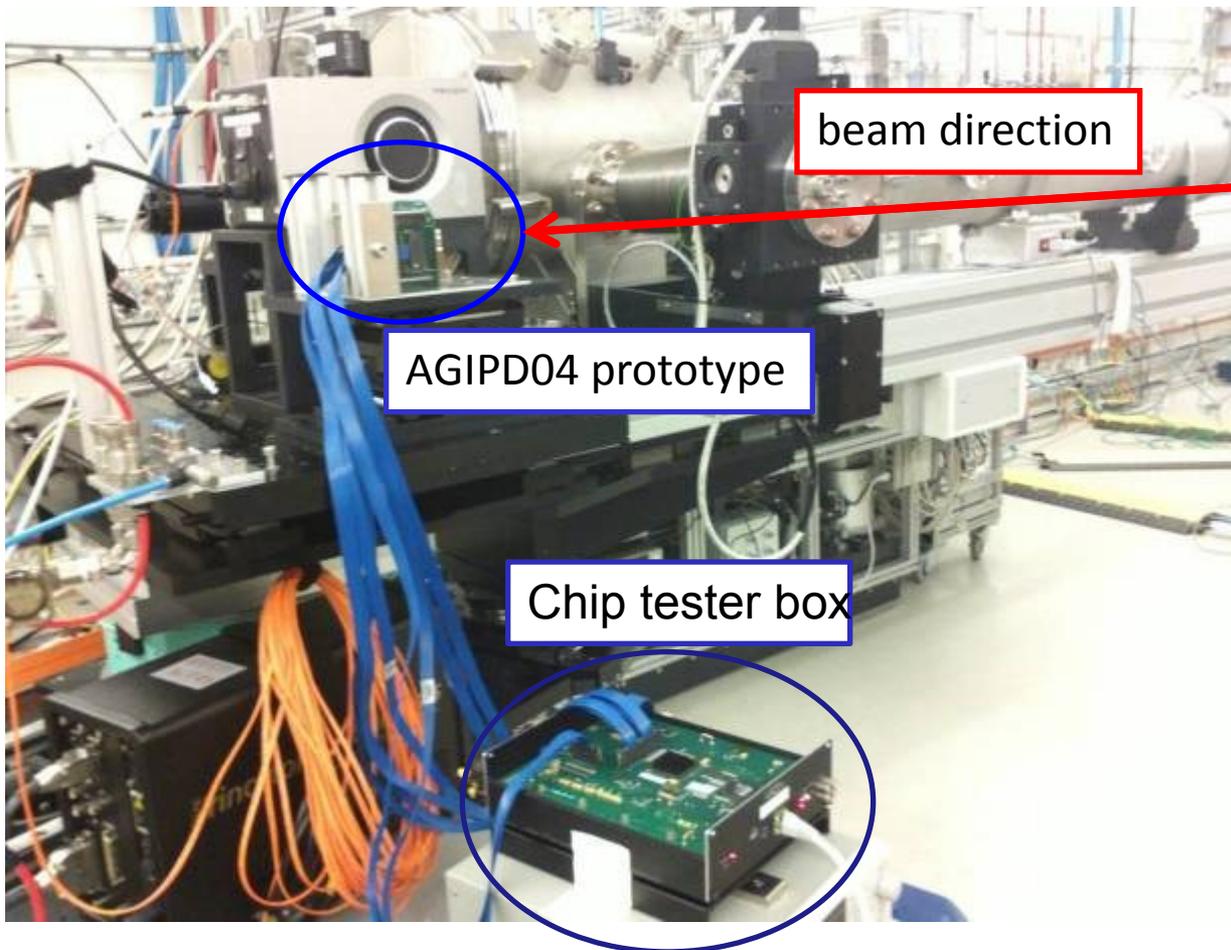
pixel current (< 0.2 nA) saturates for doses above 1 MGy

No breakdown up to 900 V after 10 MGy (and expected for even higher doses)

C_{int} (<150fF) weakly dependent on dose



AGIPD at Petra P01/10

The logo for AGIPD, featuring the letters 'AGIPD' in a bold, black, sans-serif font inside a stylized eye shape with a grid pattern.

beamline P01
Energy 14.4125 keV
(high res. monochrom.)
192 ns/bunch
triggered acquisition
no sample

beamline P10
Energy 7.05 keV
 $\sim 1.7 \times 10^{11}$ photons/sec,
60 bunch mode (128 ns)
auto acquisition
200ns & 192 ns integr.
2 samples: SiO₂
particles in liquid
(100 & 250 nm radius)

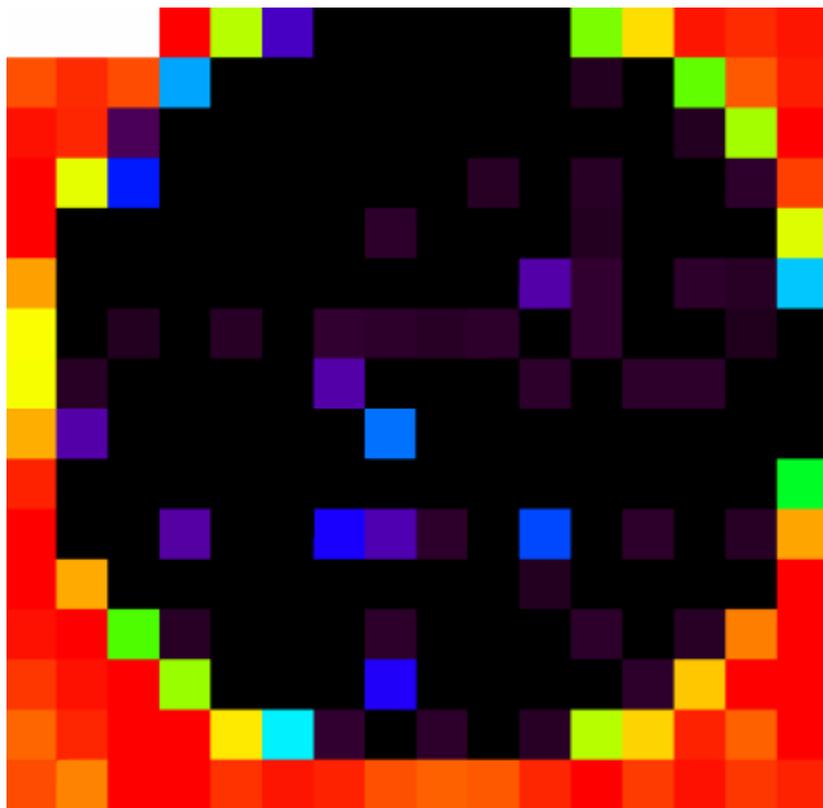
Not in the picture: Sample,
control PC, me pushing buttons, ...



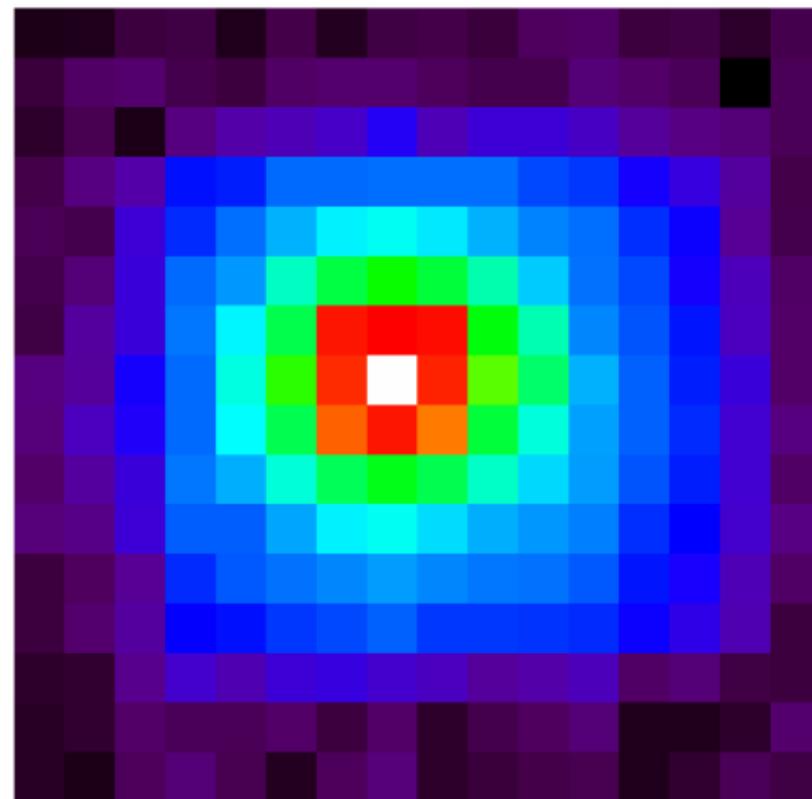
AGIPD at Petra P10



beam stopper



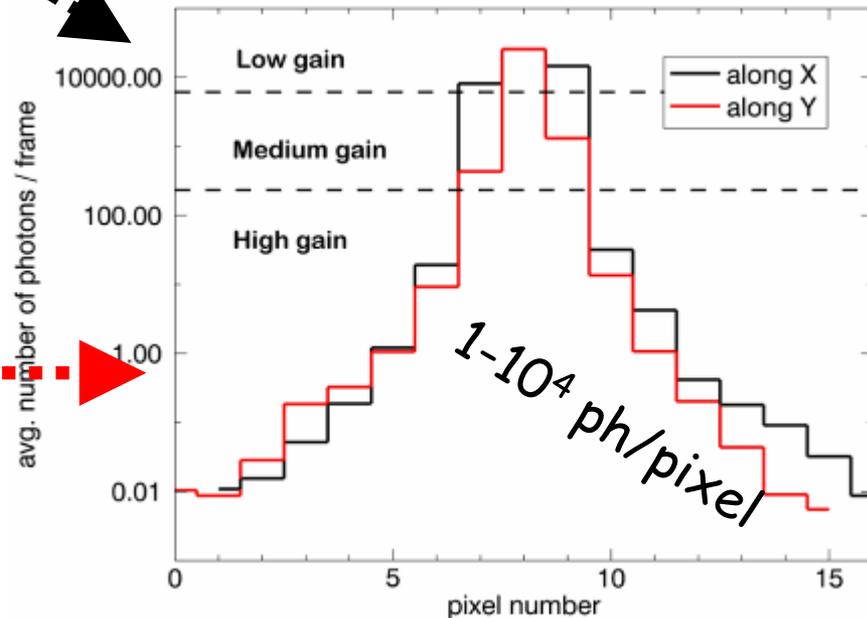
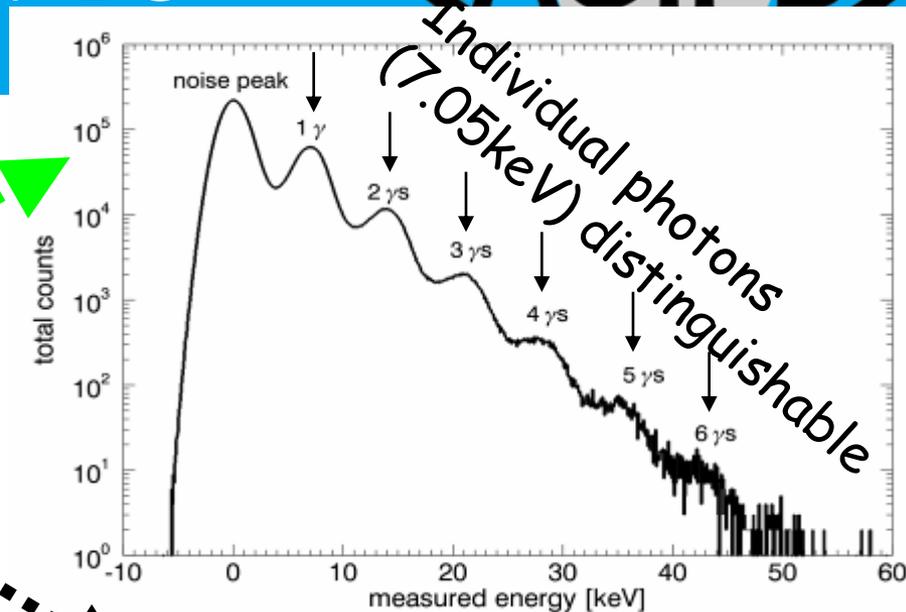
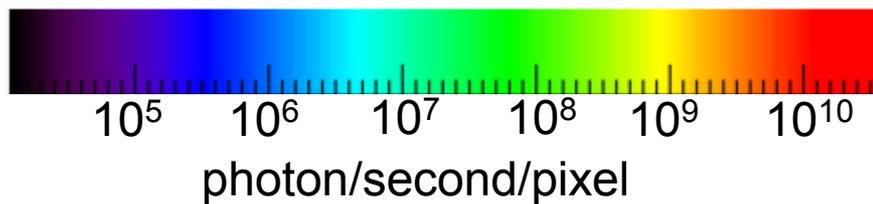
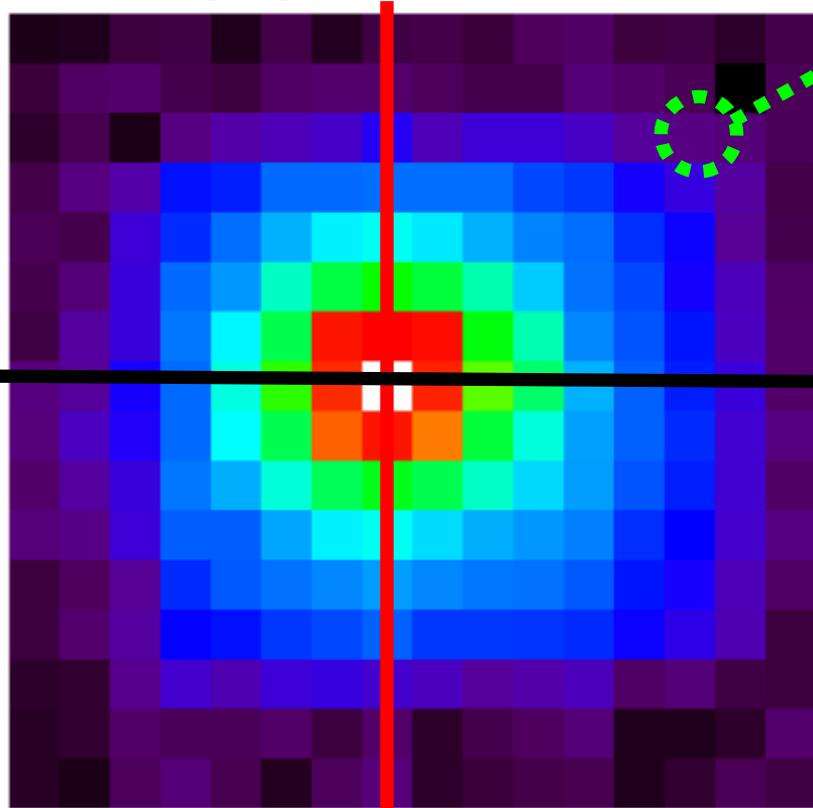
imaging the direct beam



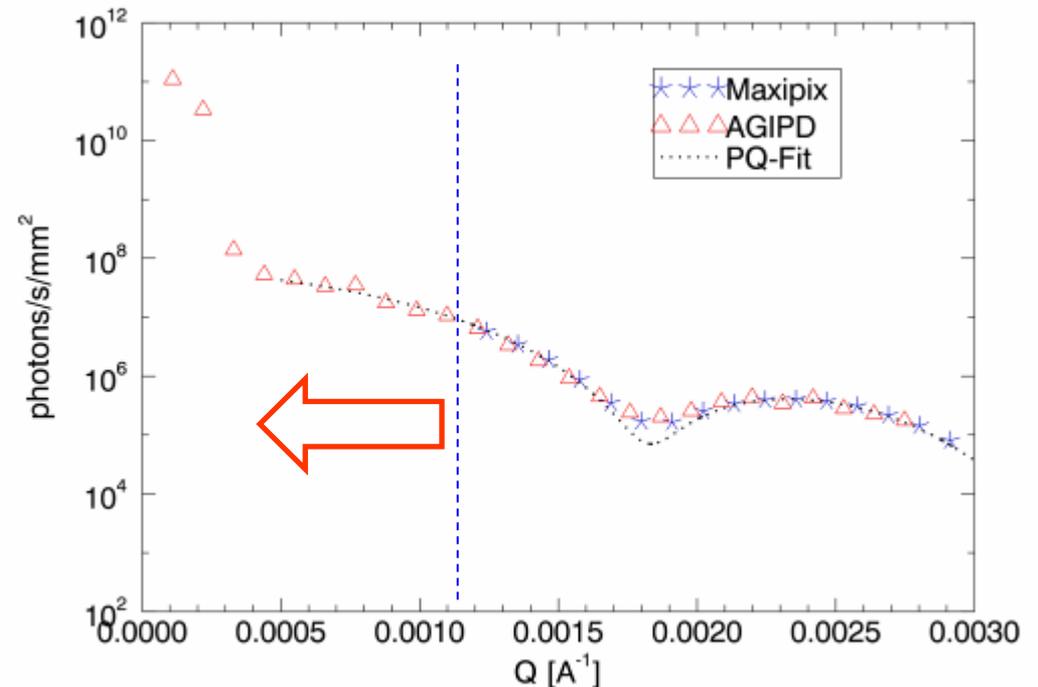
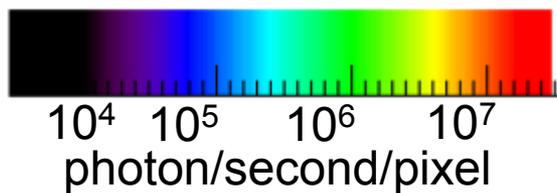
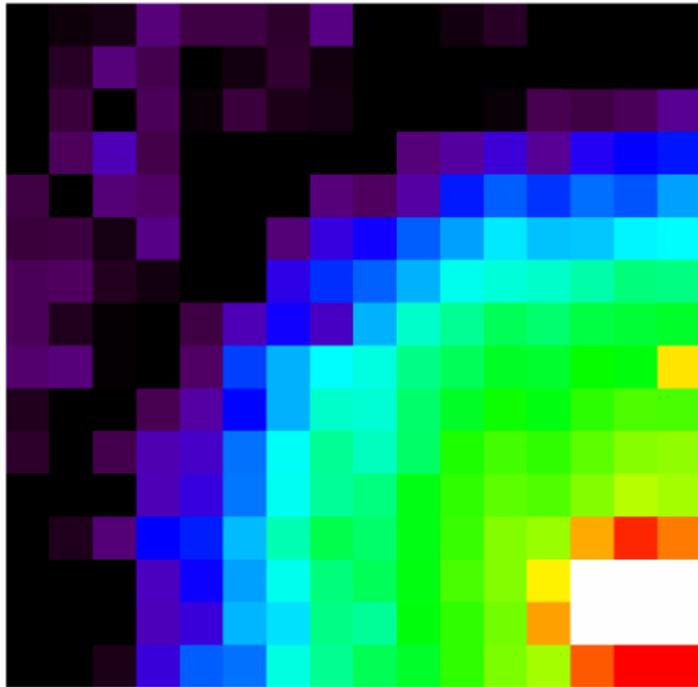
AGIPD at Petra P10



imaging the direct beam



AGIPD at Petra P10



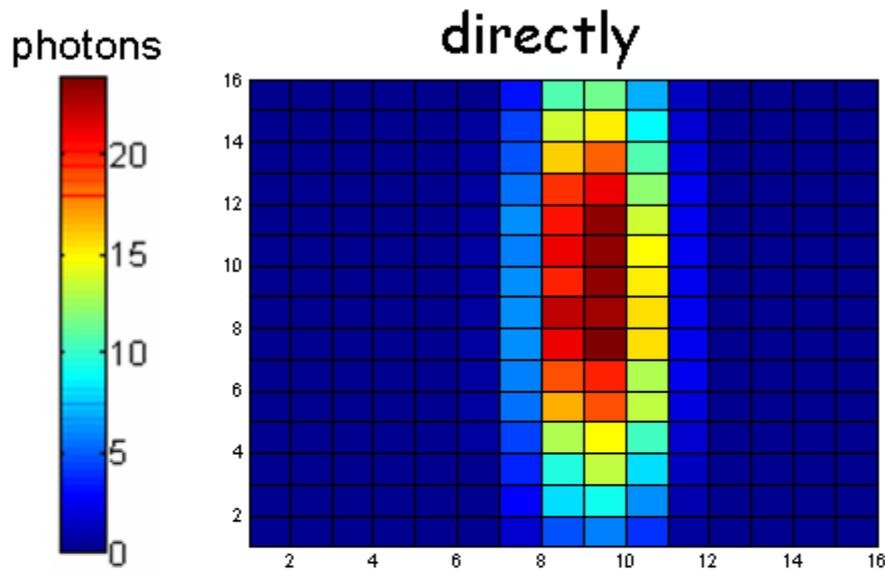
X-ray Photon Correlation Spectroscopy exp. results comparable to estab. detectors extending the range (no beam stop \rightarrow nearer to beam center)



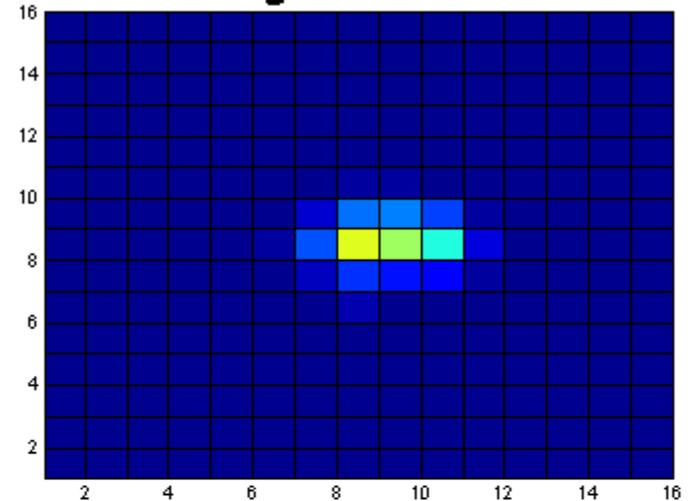
AGIPD at Petra P01



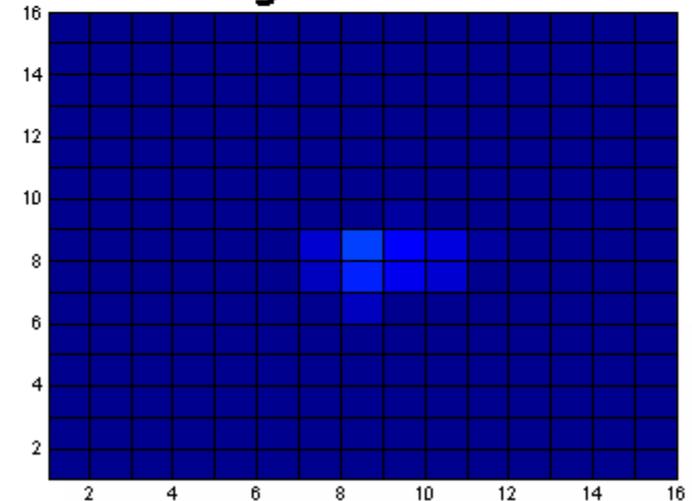
imaging the direct beam (14.4keV)



through 150um slit

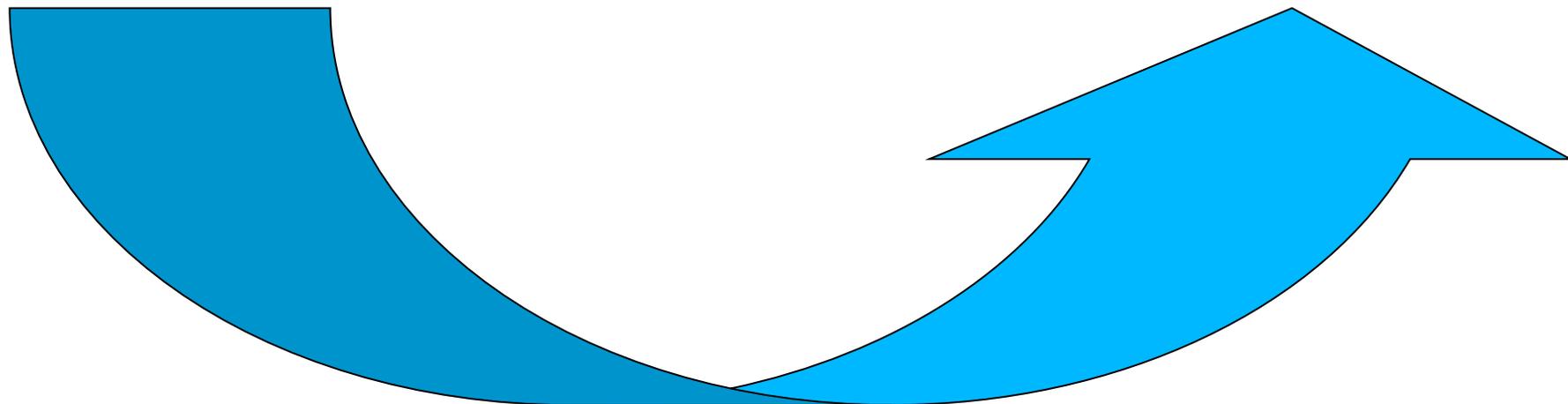


through 50um slit



used to perform measurements of
intensity correlations in the beam

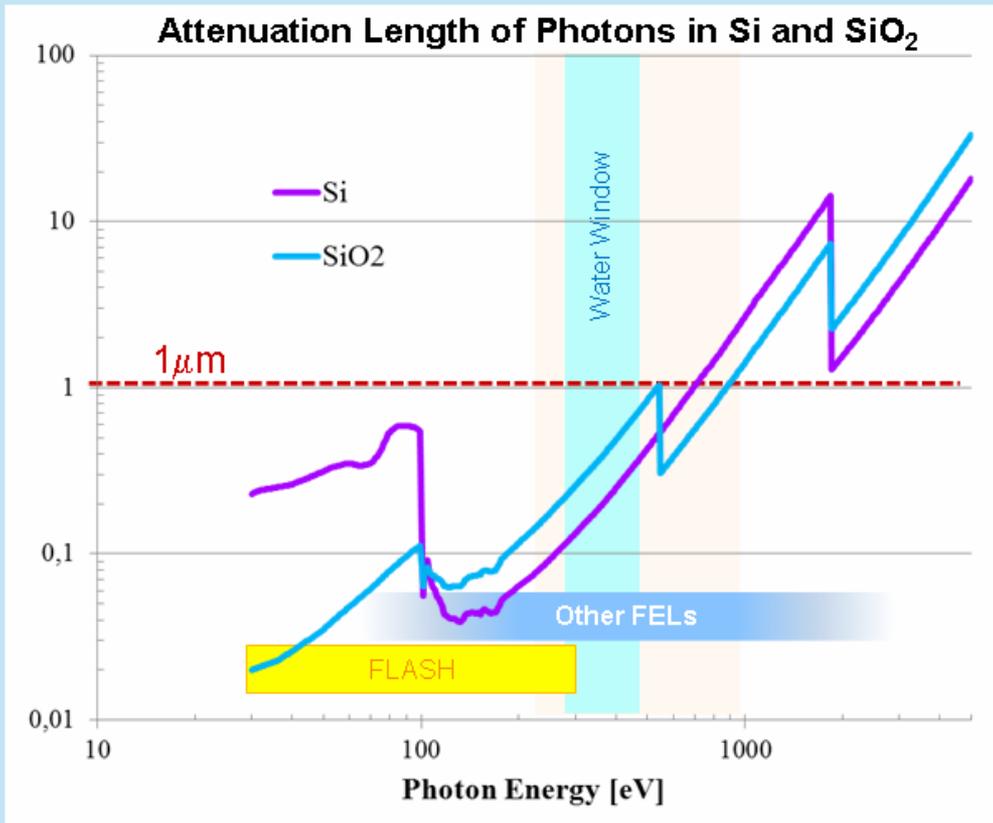
*High order interferometry of single storage
ring pulses measured by AGIP detector
A. Singer, I. A. Vartanyants et al.
[subm for pubbl.]*



What about lower energy photons?



Percival: Motivation

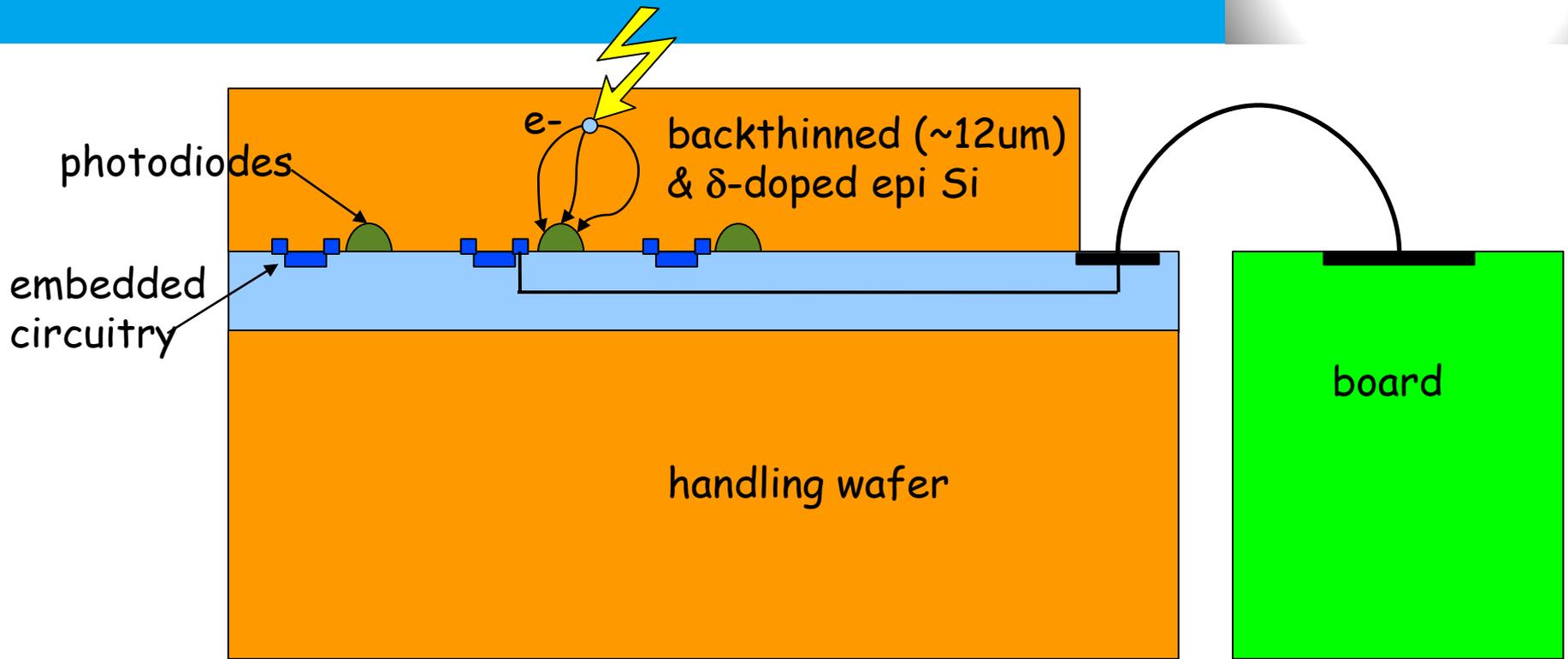


data from CXRO database

- 1-photon resolution!
- 250 eV - 1 keV!
- high dyn range!
- 85-95% QE!
- many pixels! small pixels!
- 2-side buttable! (even more pixels)

Challenge below 1keV:
sub-um absorption lengths





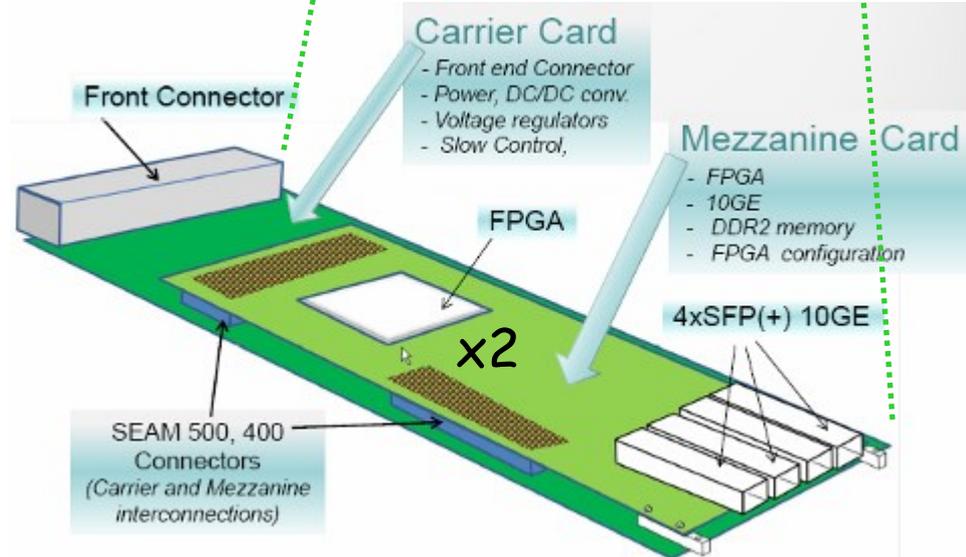
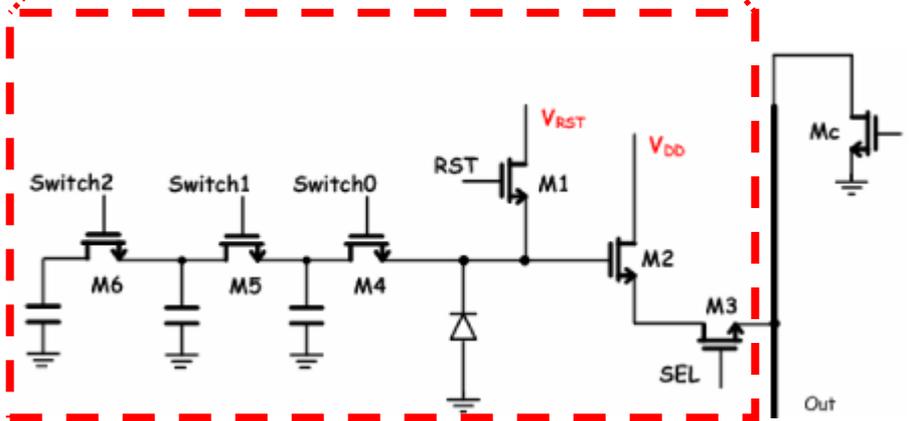
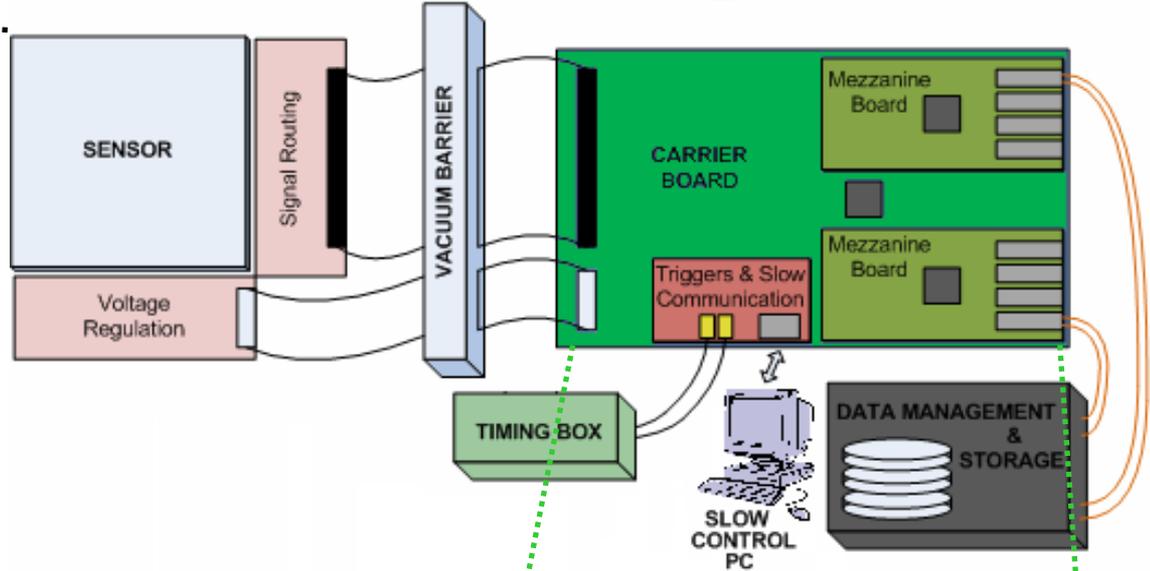
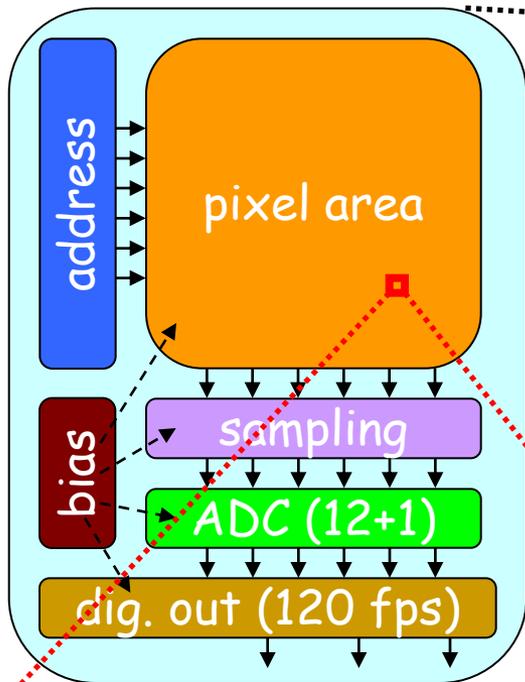
Monolithic: Collecting diodes & readout circuitry share the same substrate
Fast rise in the last ~ 10 yrs, today the common technology in digital cameras.
Using standard industrial CMOS processes

Gain from industry developments, shrinking feature sizes, ...

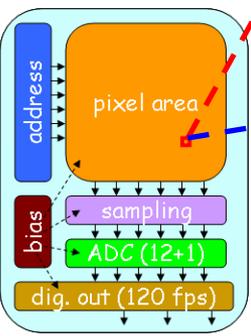
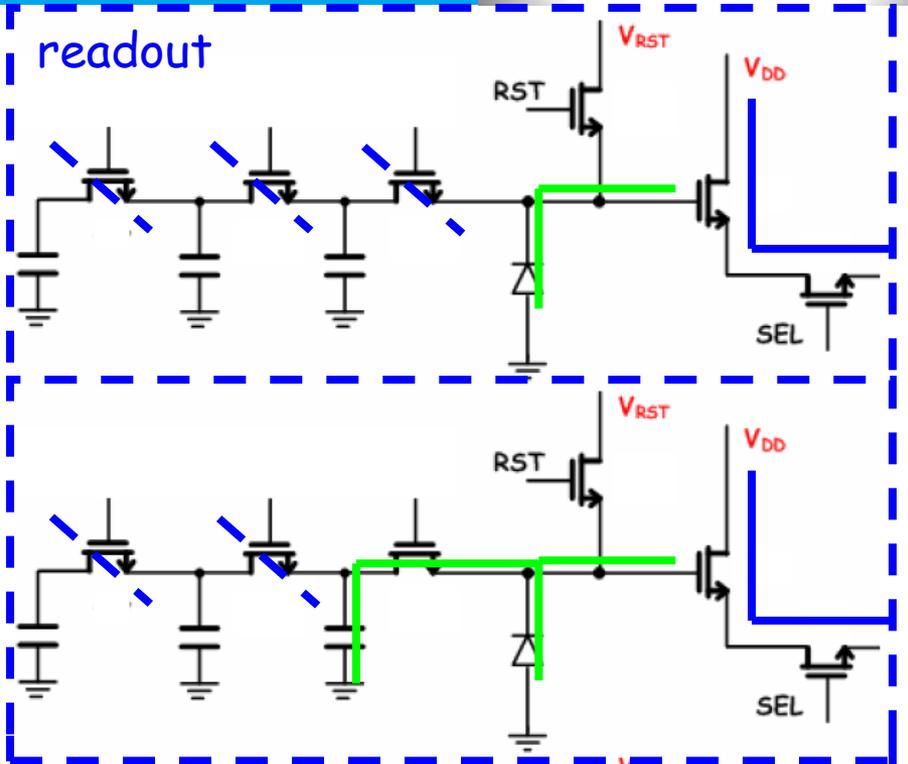
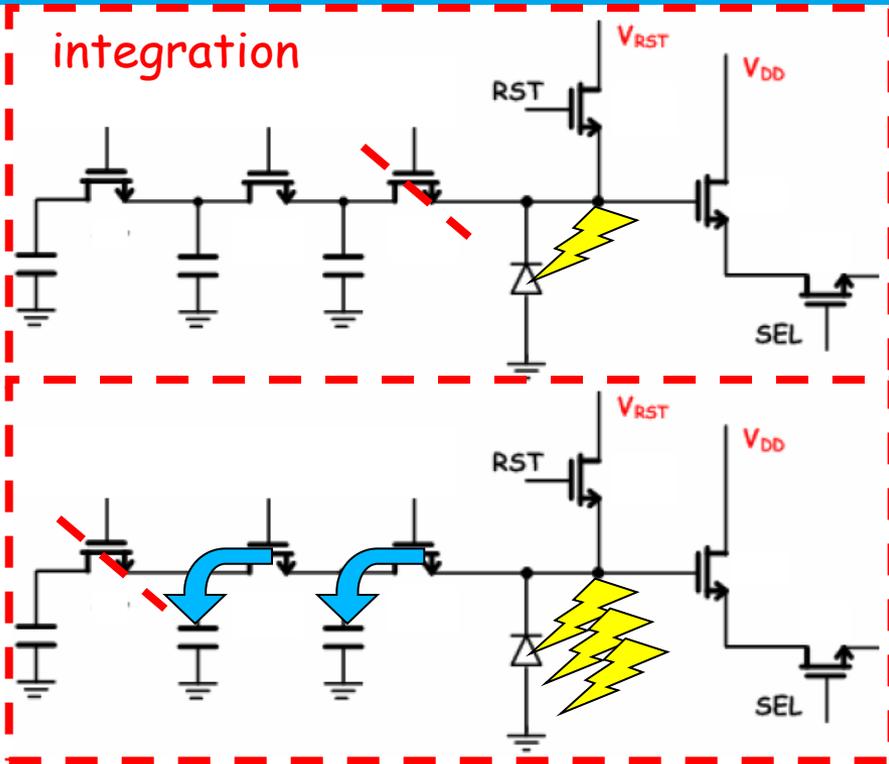
Limitations imposed by commercial foundries:
epilayer thickness, V constraints



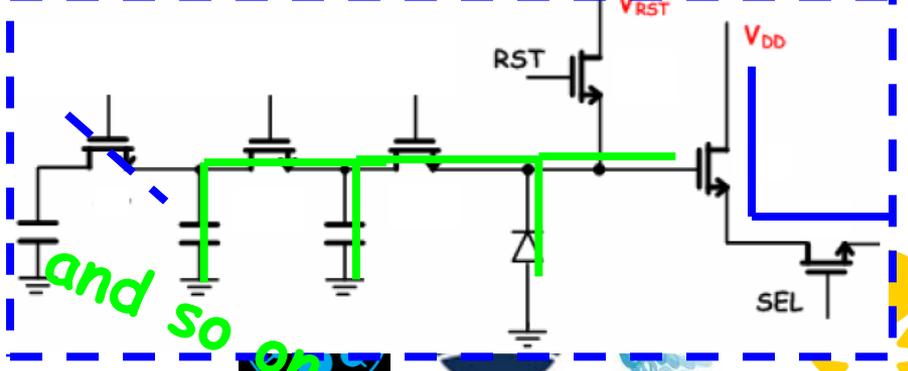
The P.E.R.C.I.V.A.L.(1)



multiple gains: a different approach



Modified 3T pixel architecture
High dynamic range achieved with multiple readings and lateral overflow



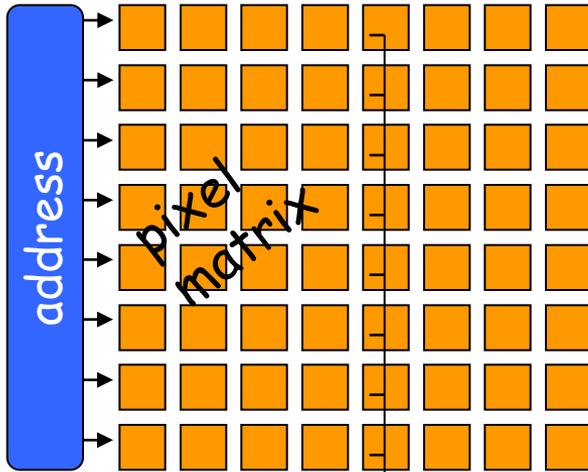
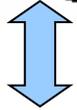
and so on



The P.E.R.C.I.V.A.L.(2)



slow control PC

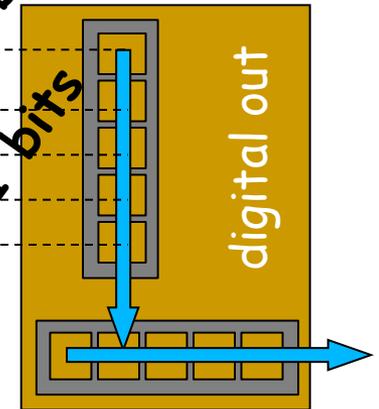
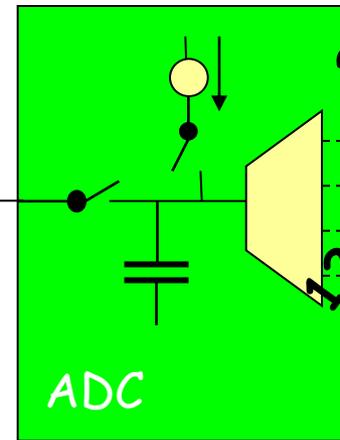
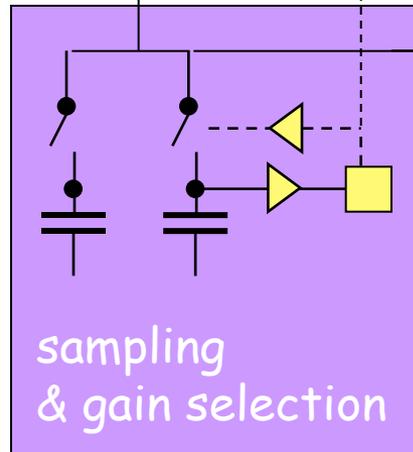


10~16M pixels
x 15 bit/pixel
x 2 (double sampling)
x 120 frame/s

36~58 Gbit/s

double sampling (of reset level & integrated signal)

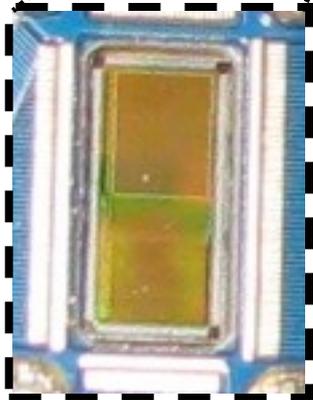
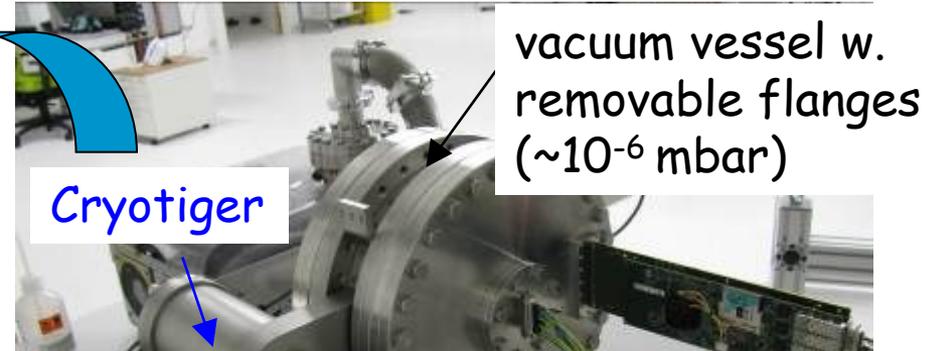
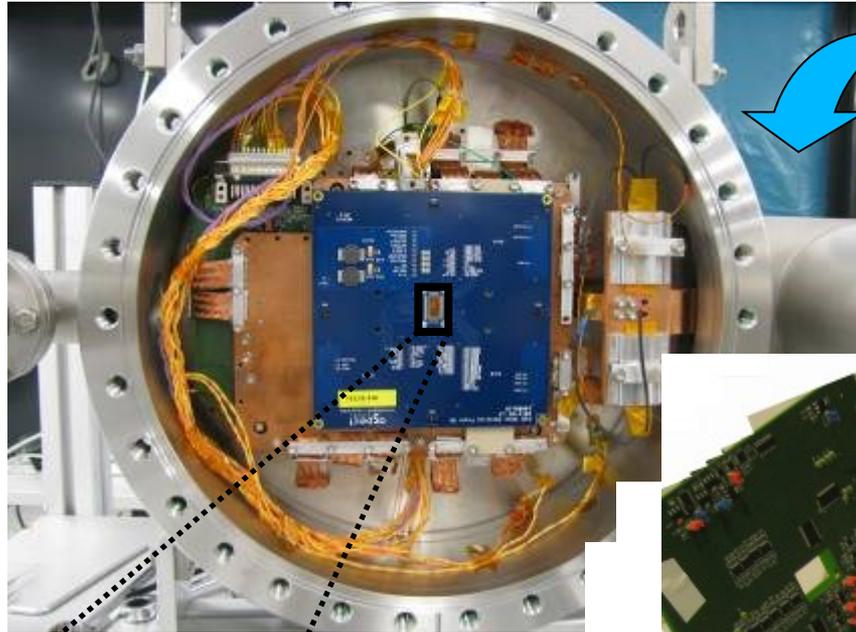
possibility of streaming out only one [the most suitable] of the multiple reading of integrated signal (+2 sel. bits)



upto 120 frame/s

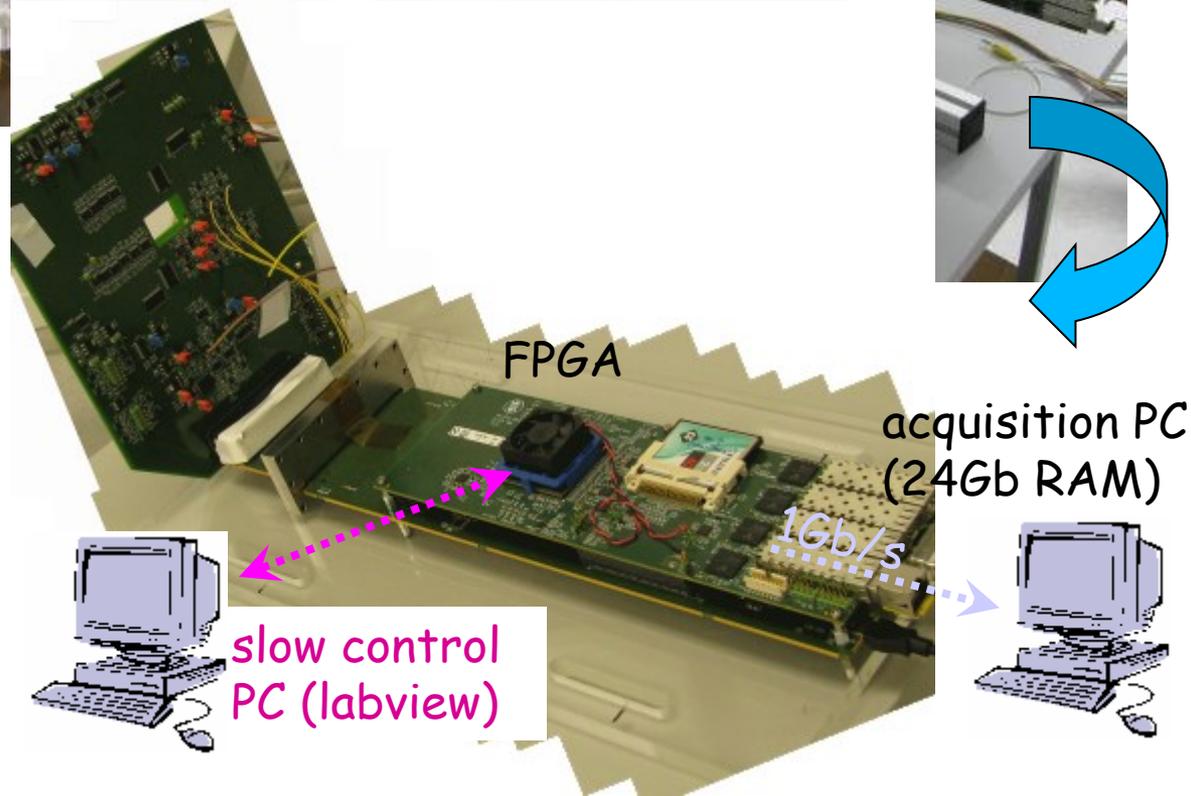


Percival Prototype (1)



210x160 pixels
(6 flavours)
25um pitch

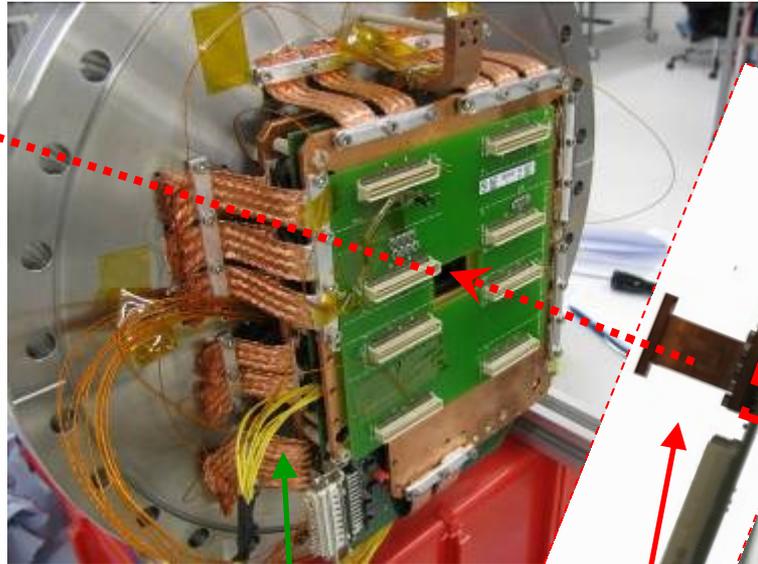
front-illuminated



Percival Prototype (2)



to low-T cooling system (cryotiger)
exp 0~-40°C



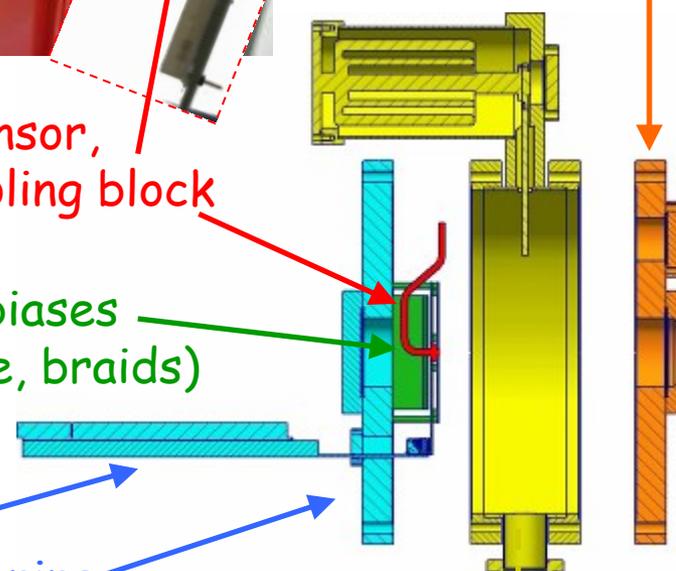
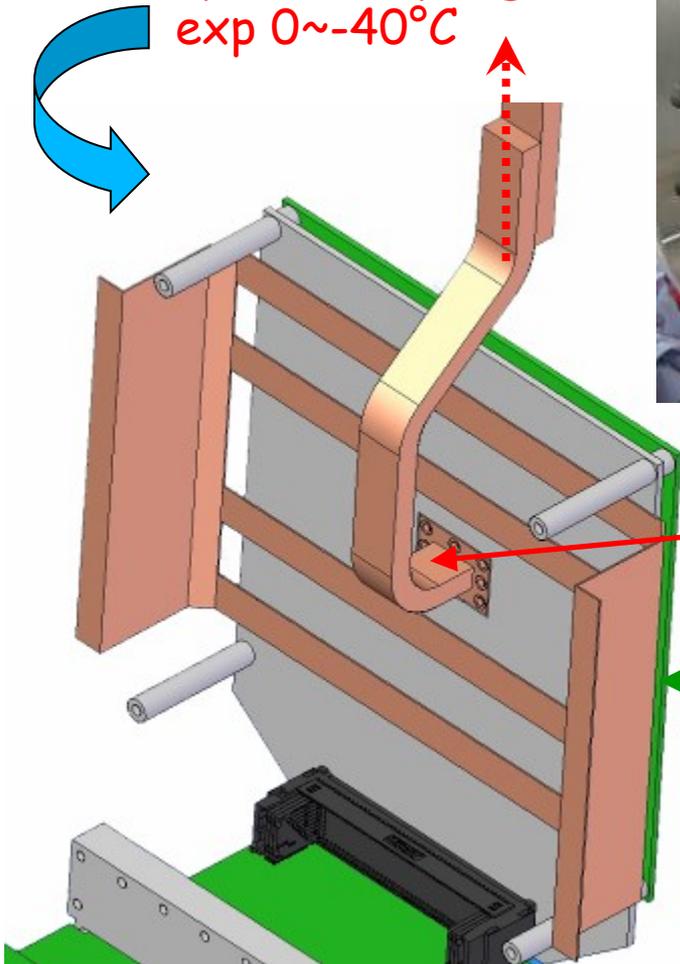
periph board
CMOS <-> LVDS, biases
~ Troom (Cu plane, braids)

Sensor,
cooling block

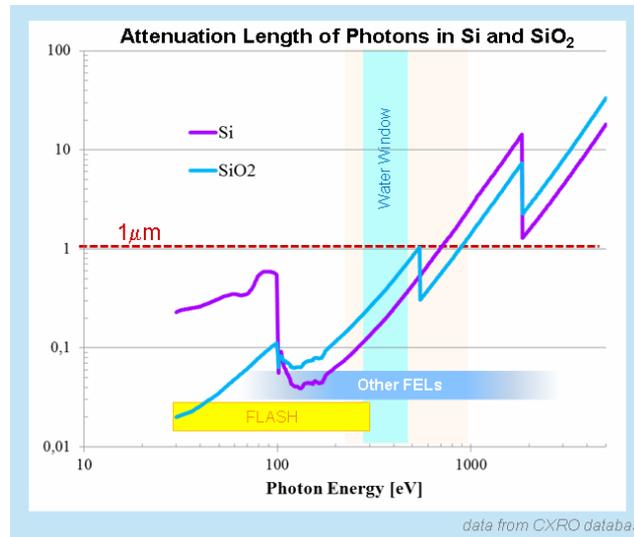
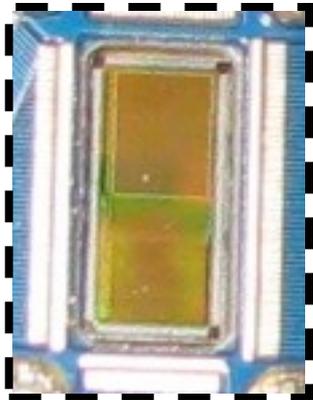
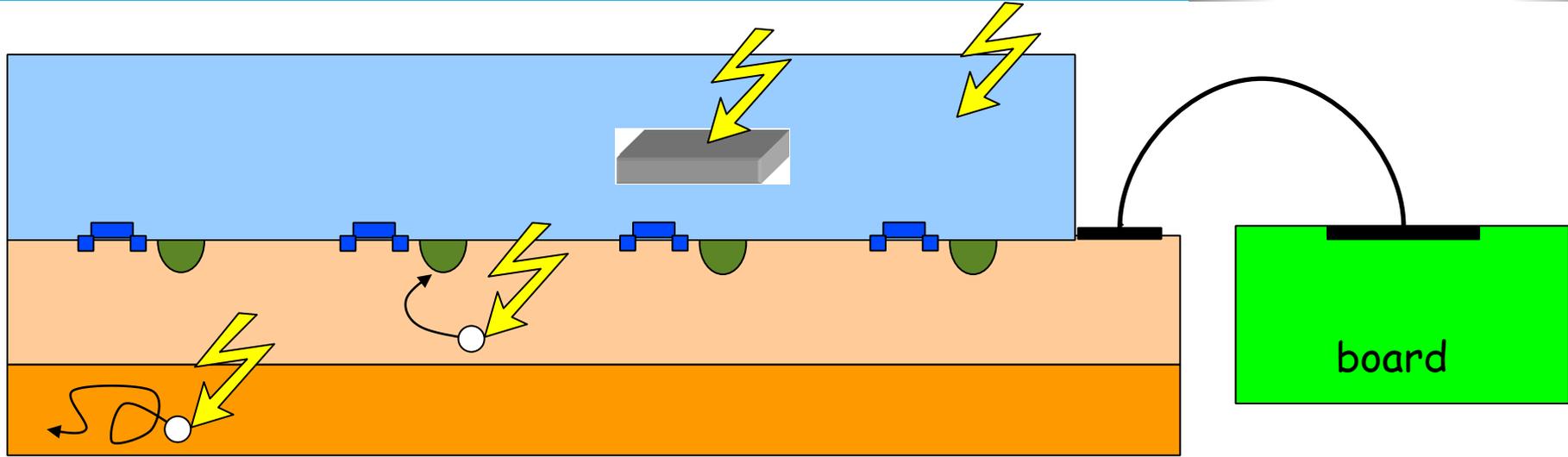
back flange
SD board, mezzanine

to vacuum pump

front flange with
beam opening



Front-illuminated limits



intrinsic limit: much charge will not be properly collected by photodiodes

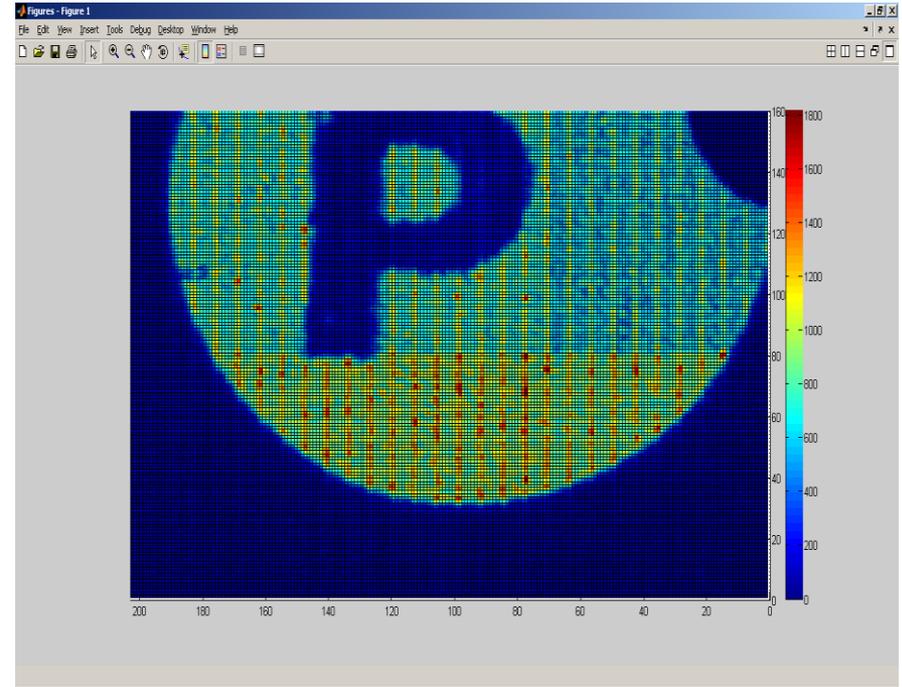
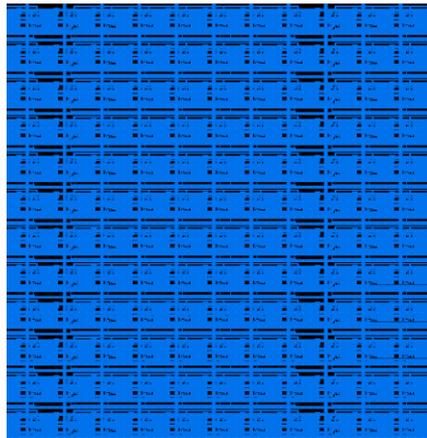
backthinned prototypes for back-illumination to be ready ~end of the year



imaging with prototype



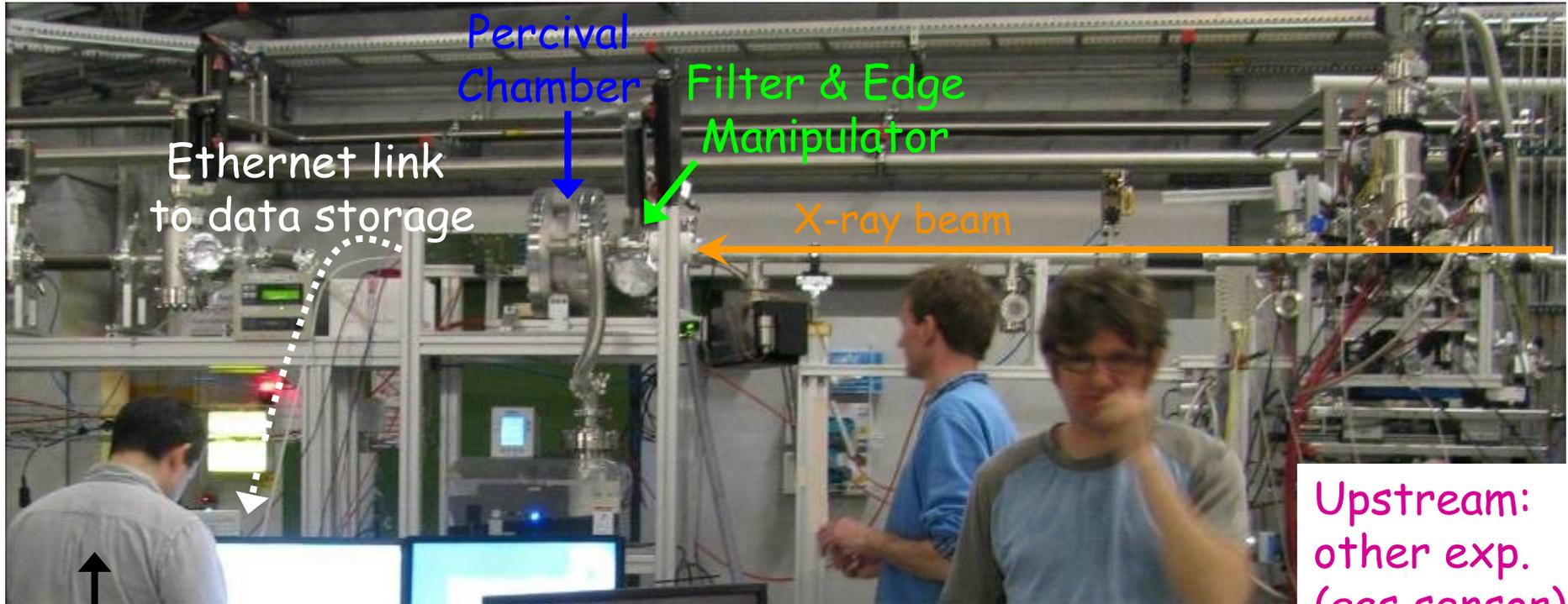
"P" laser-printed on transparent foil, mounted on circular sample holder interposed between the sensor and a white-light LED.



Vertical "stripes" due to differing metal layers modulating the incident light in front-illumination.

6 different pixel types -> different responses

Percival at Petra P04



me pushing buttons

beamline 04
Energy 300eV-2keV
 $10^9 \sim 10^{13}$ photons/sec

beamline: 193ns/bunch
we: took it slow: 17 frame/s

Upstream:
other exp.
(gas sensor)

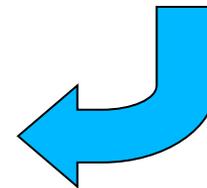
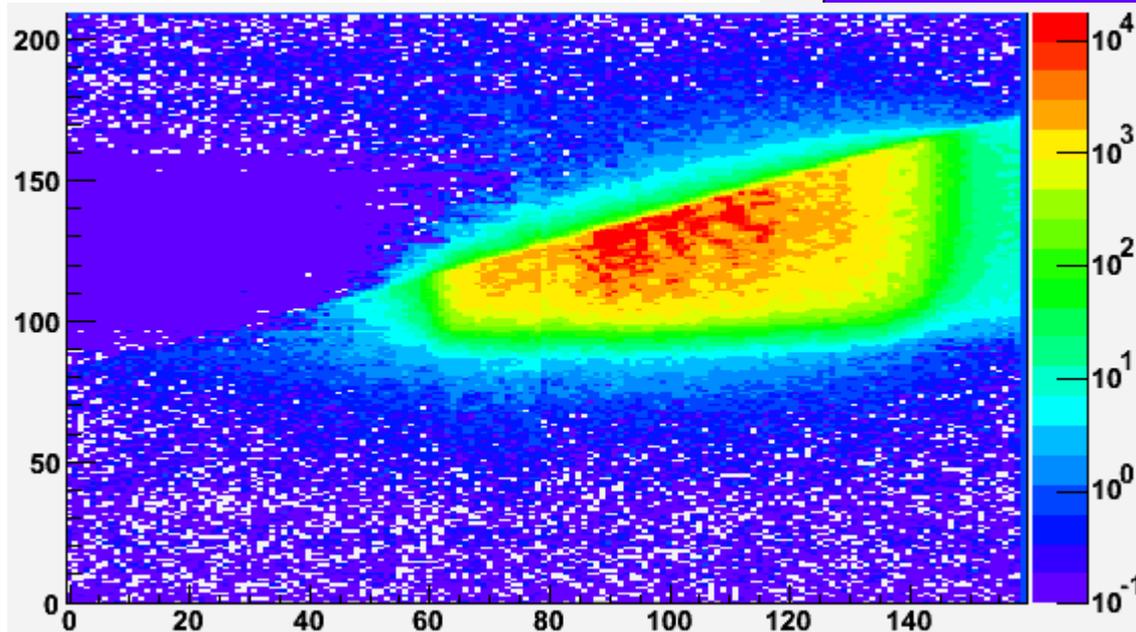
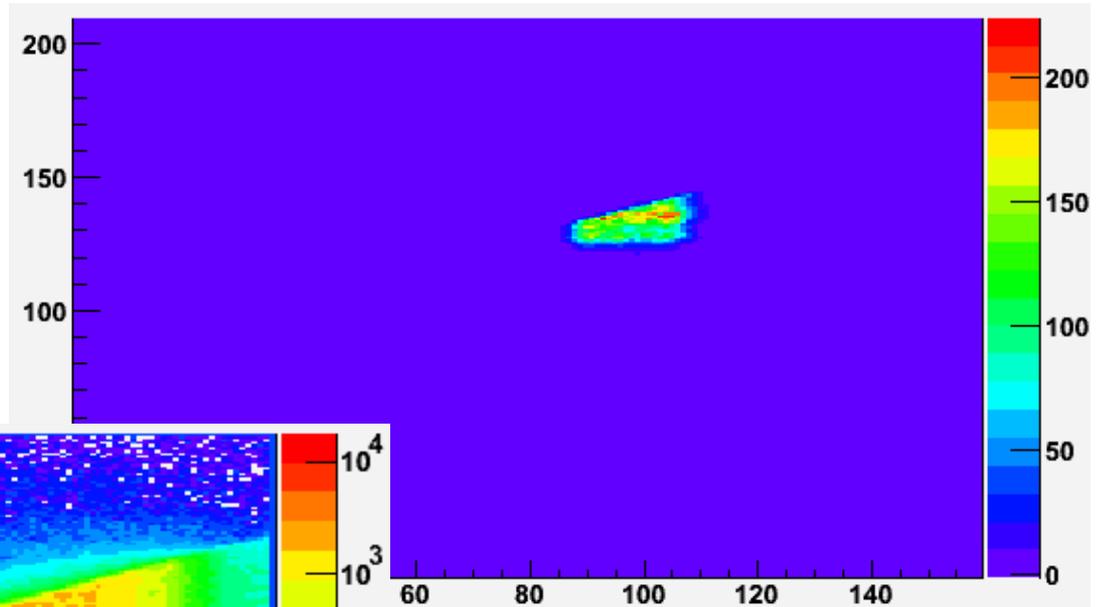
used parasitically
(downstream gas detectors)



Percival at Petra P04

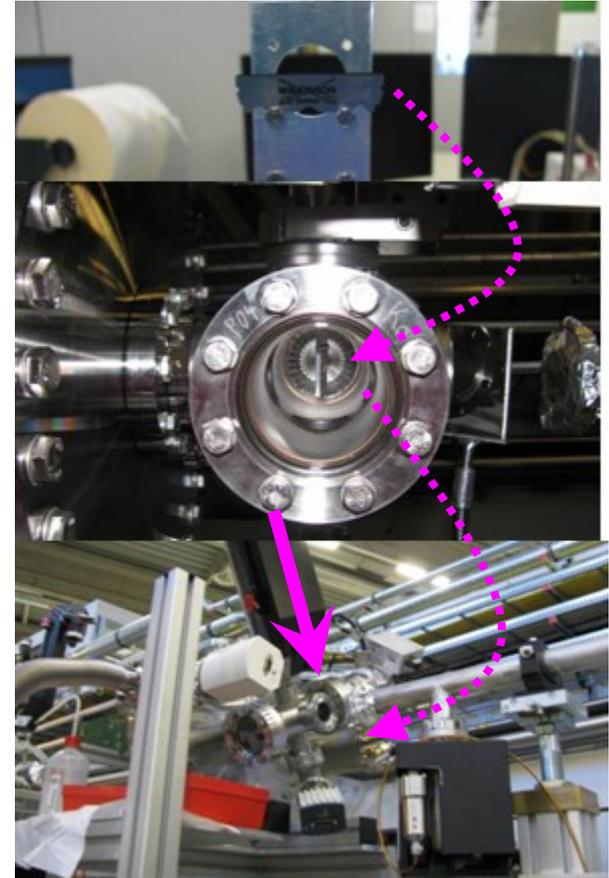
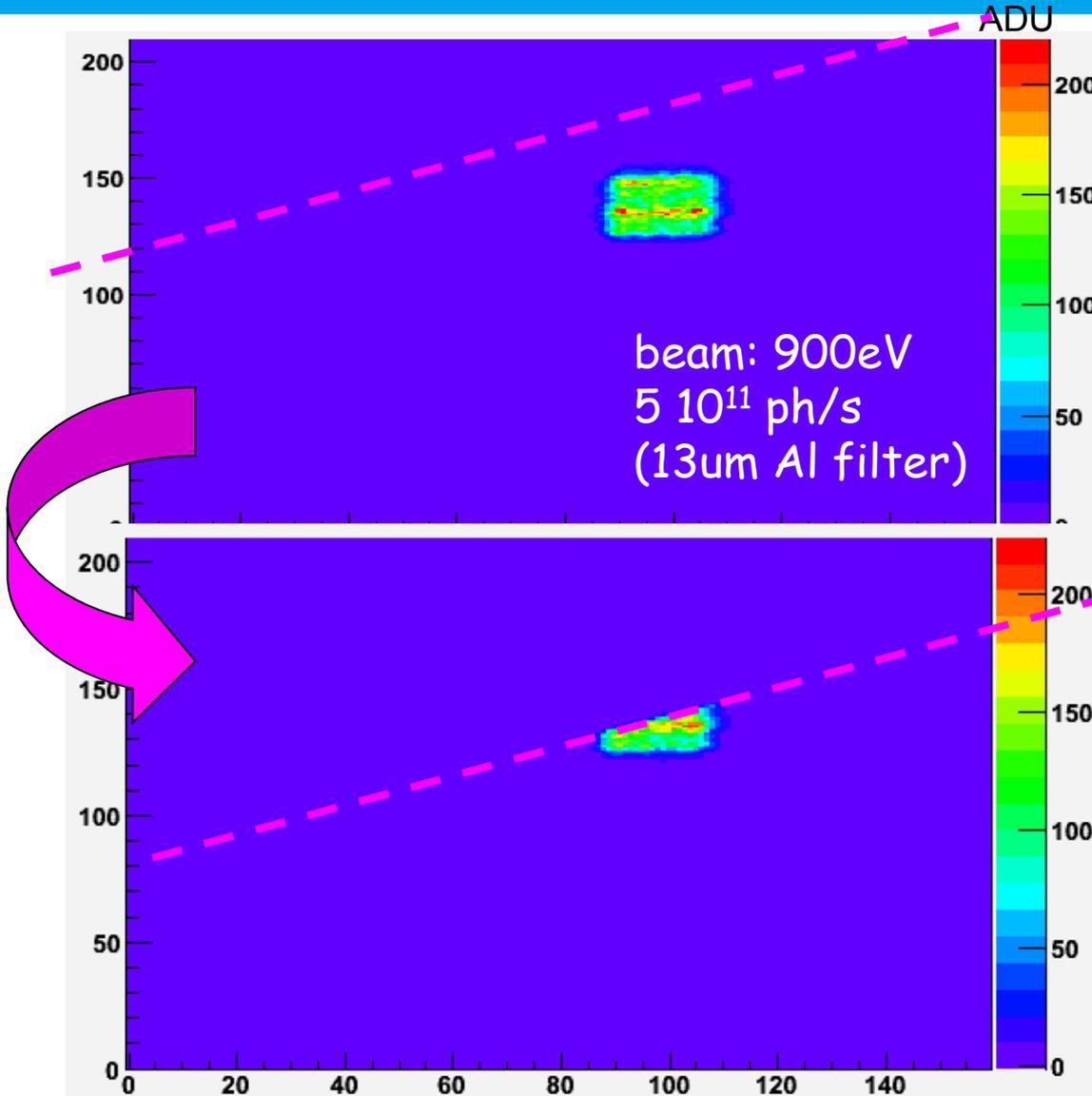


beam: 900eV
 $5 \cdot 10^{11} \rightarrow \sim 5 \cdot 10^{13}$ ph/s
(13um Al filter)

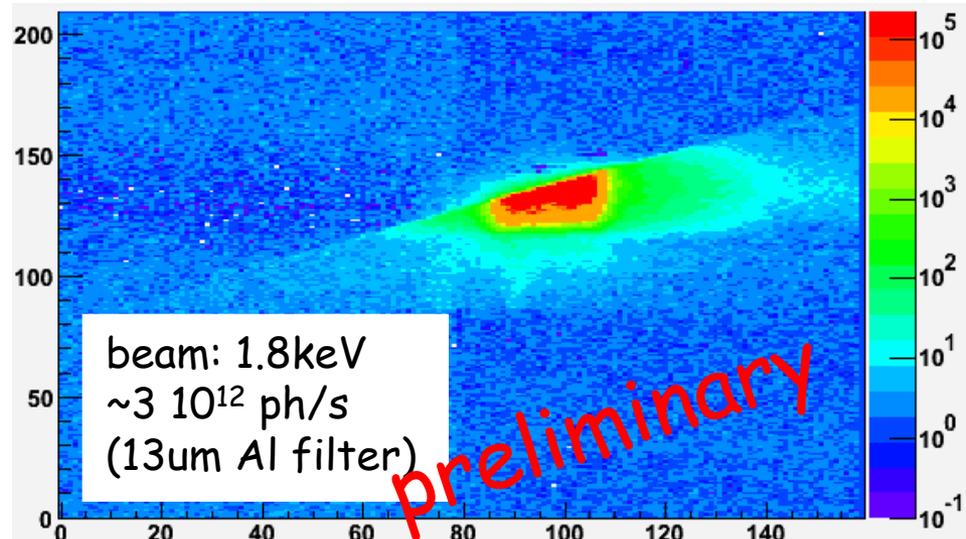
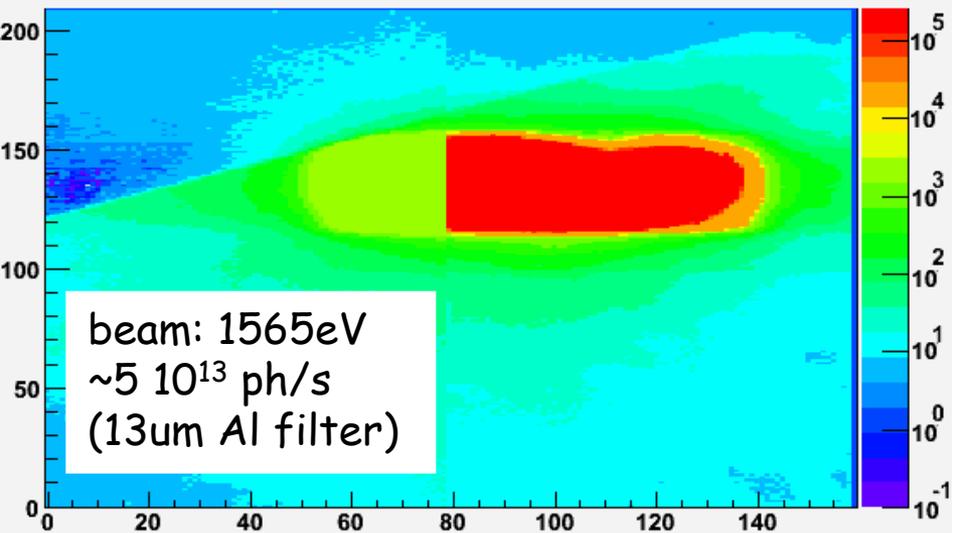
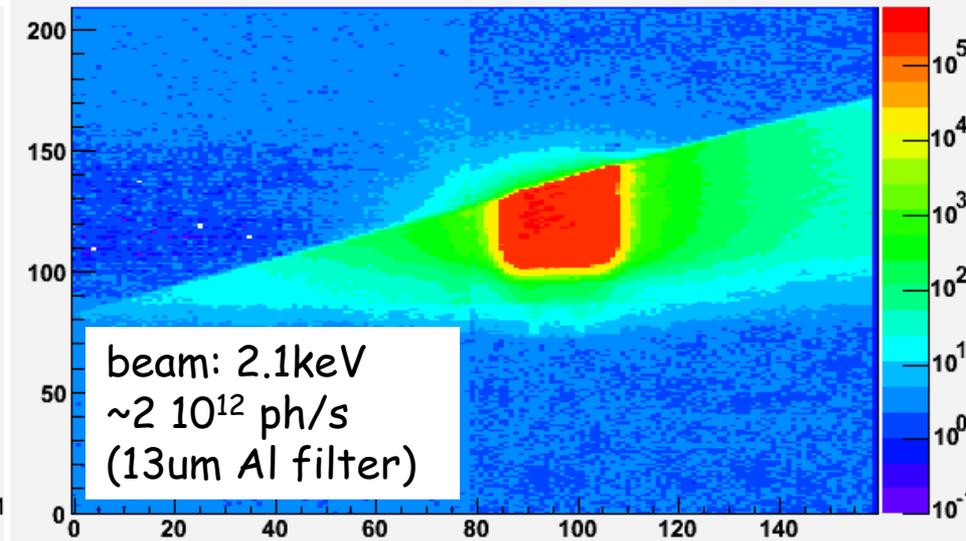
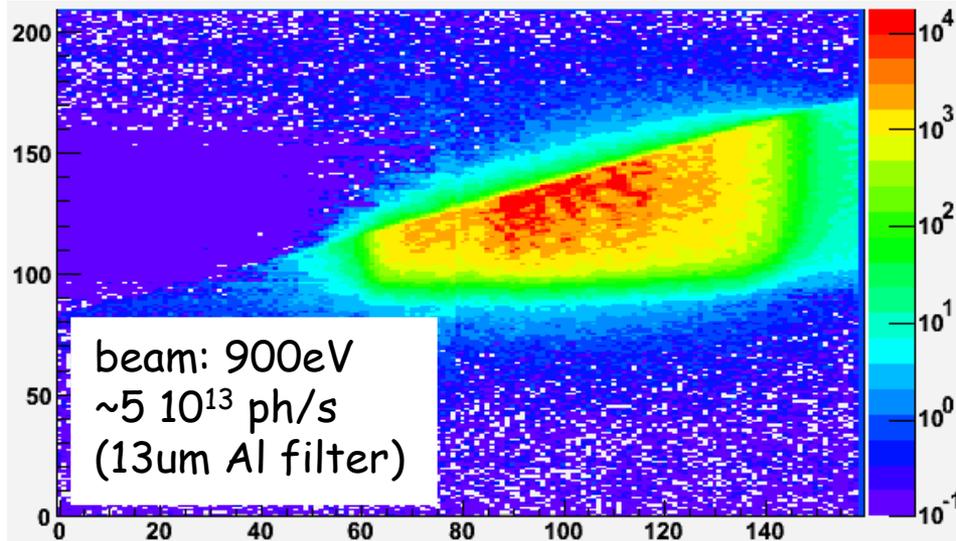


preliminary

Percival at Petra P04



Percival at Petra P04





Summary



A.G.I.P.D.

- 1Mpixel, 200um pitch
- ~12keV photons [7~14 tested]
- single photon upto $\sim 10^4$ photons/pixel/frame
- 300e noise: tested
- 4.5 Mframe/s (burst): tested 5.2
- Single chip assemblies: in a few weeks
- First 1M system: beginning 2015

P.E.R.C.I.V.A.L.

- prototype ~ 33 kpixel 25um
- preliminary test on front-illuminated samples 900eV \sim 2keV
- Back-thinned test structures end of 2013 \rightarrow soft X-ray testing (250eV \sim 1keV photons)
- Full sensor [10 \sim 16Mpixel, 25 \sim 27um pixel pitch] tape-out 2014
- First full, back-thinned sensor ready for X-rays 2015





backup



The A.G.I.P.D. (1_{data} out)



pixels 1M
 mem cell/pixel x 352
 analog & gain x2
 bits/sample x 14
 in 100ms x10

 avg data rate ~96.5Gb/s

then why 16 mezzanines,
 each with 4x10Gb/s outs?

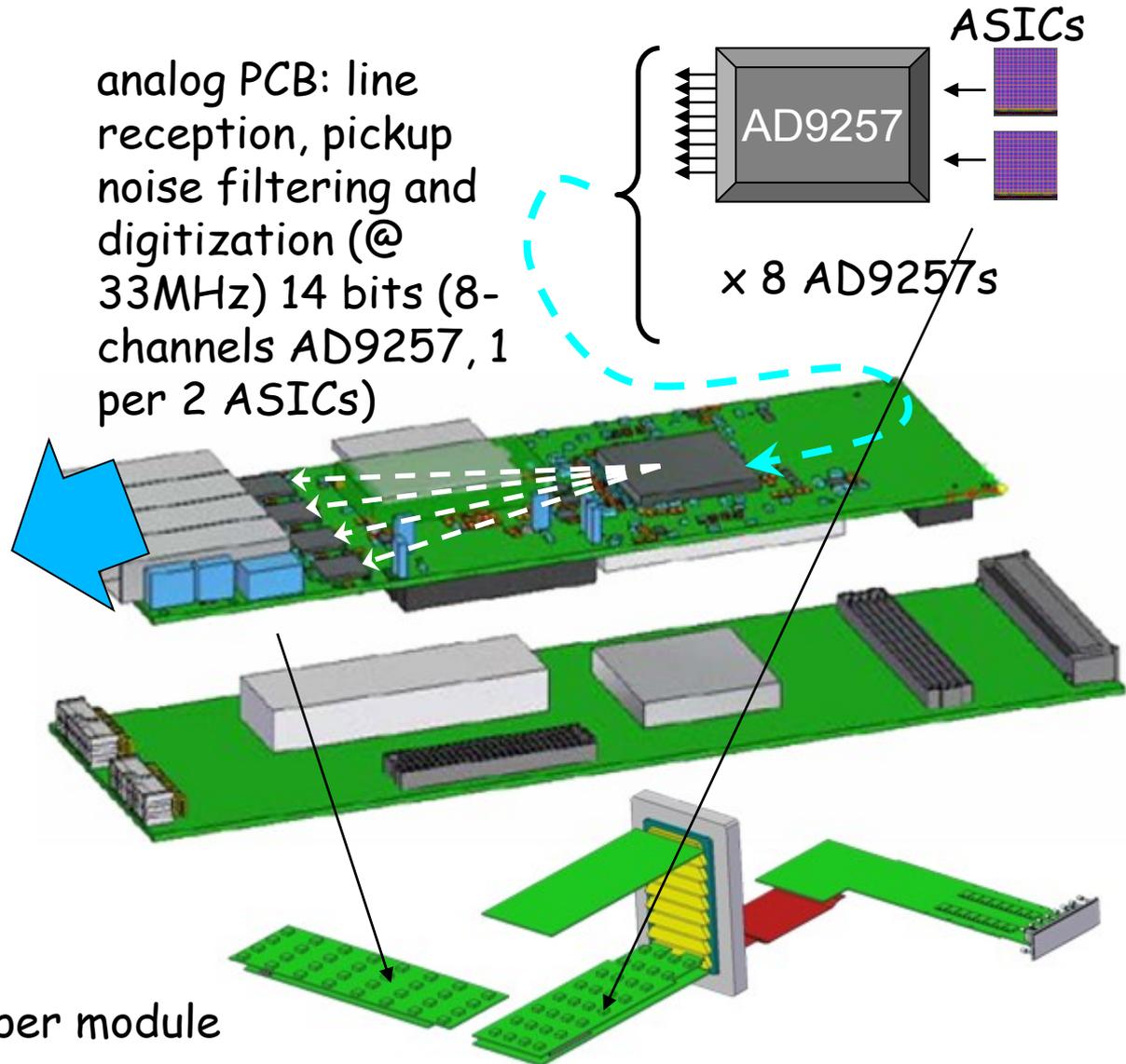
common development with
 other projects

limited FPGA memory per
 mezzanine (resorting)

ADC out/module 8 x 8
 sampled at x 33Mhz
 bits/sample x 14

 burst data rate ~29.5Gb/s per module

analog PCB: line
 reception, pickup
 noise filtering and
 digitization (@
 33MHz) 14 bits (8-
 channels AD9257, 1
 per 2 ASICs)



irradiating ASIC (2)

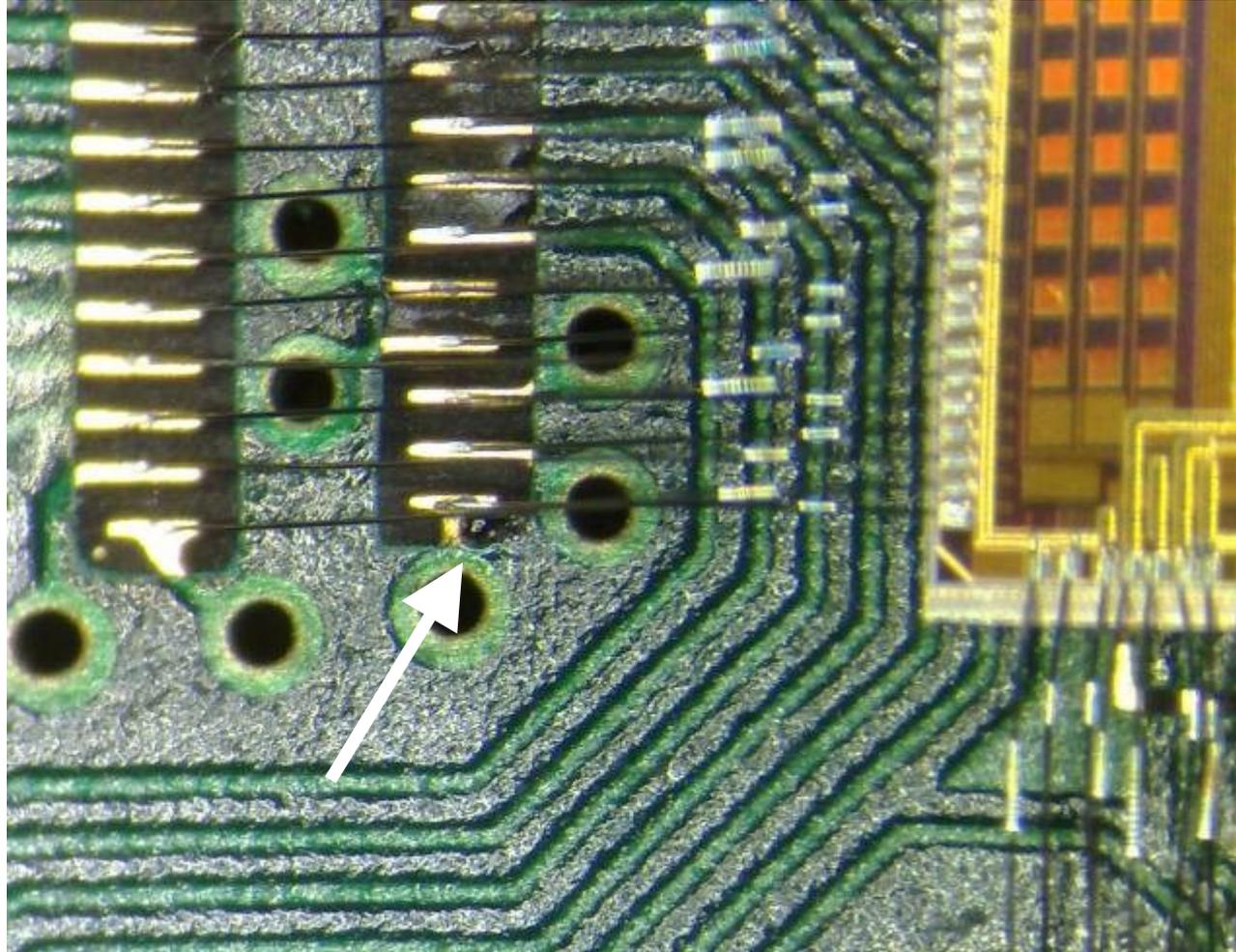


first irradiation attempts (ASIC on FR-4) gave us troubles:

12-24h after ($\sim 10\text{MGy}$) chip irradiation, FR-4 begins to sprout bubble of liquid.

if one of said bubbles forms under a wire-bond pad, the wirebond (on the FR4) fails

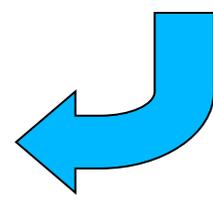
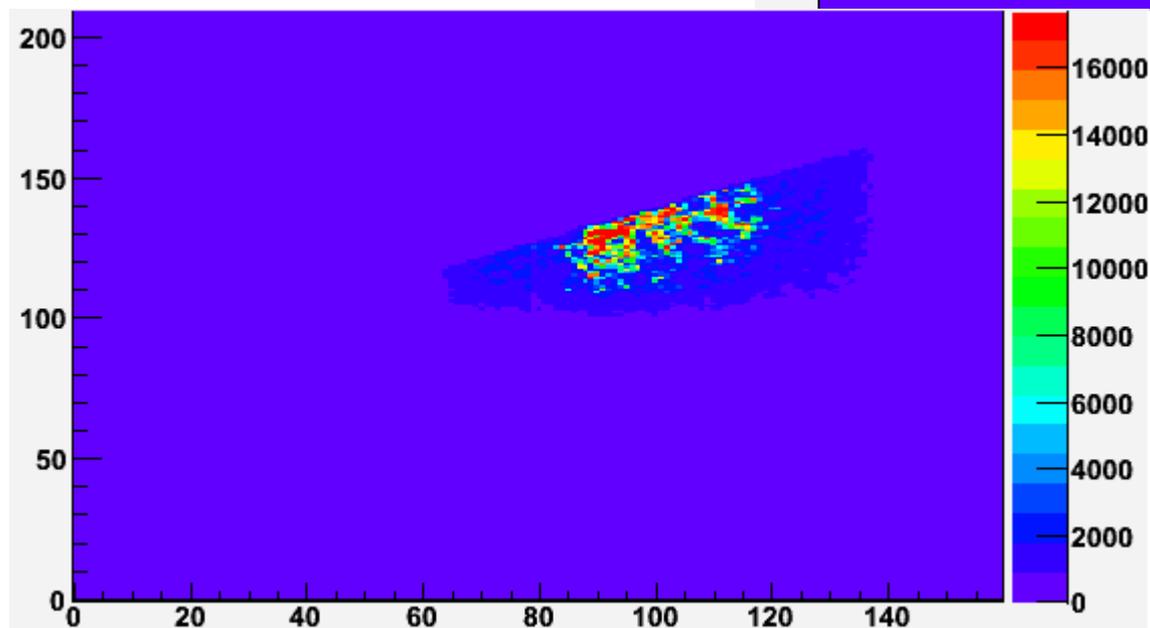
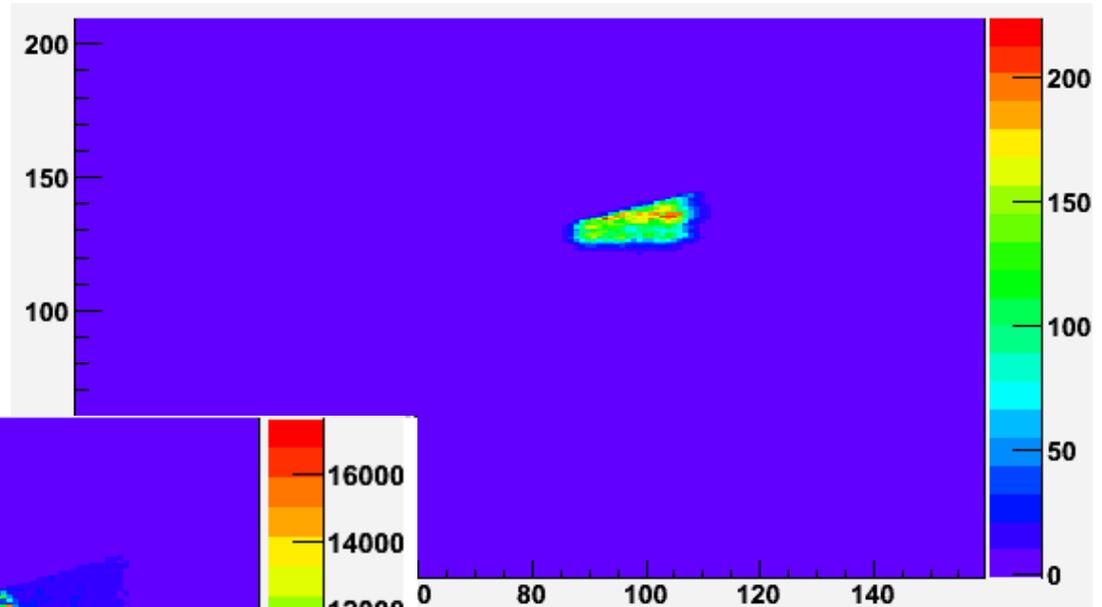
summary: use ceramics



Percival at Petra P04



beam: 900eV
 $5 \cdot 10^{11} \rightarrow \sim 5 \cdot 10^{13}$ ph/s
(13um Al filter)



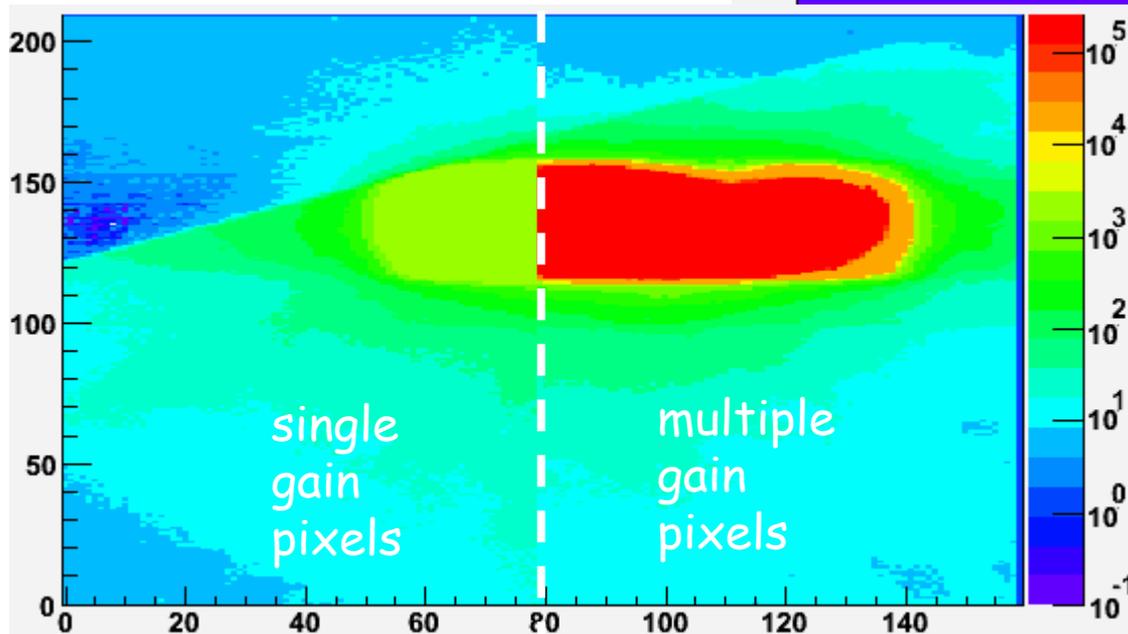
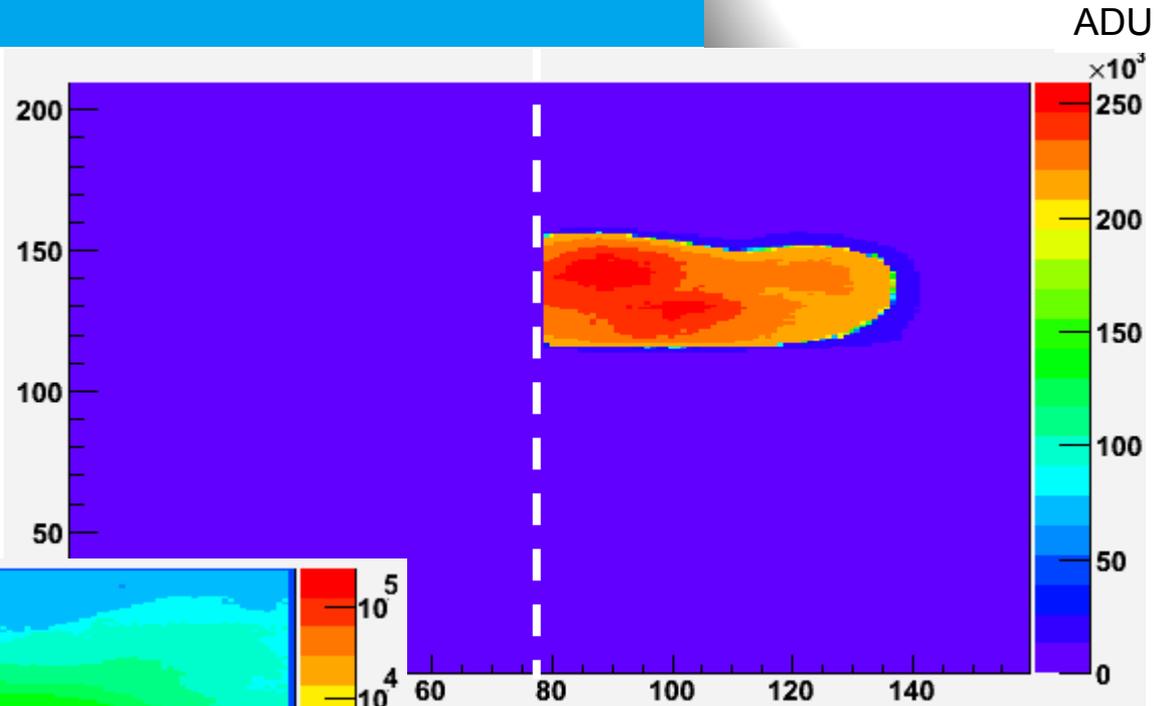
preliminary



Percival at Petra P04



beam: 1.565keV
~5 10^{13} ph/s
(13um Al filter)



ADU



preliminary

Percival at Petra P04

